RENESAS

RL78/G11

RENESAS MCU

Datasheet

R01DS0282EJ0260 Rev.2.60 Mar 29, 2024

True low-power platform (58.3 μ A/MHz, and 0.64 μ A for operation with only LVD) for the general-purpose applications, with 1.6-V to 5.5-V operation, 16-Kbyte code flash memory, and 33 DMIPS at 24 MHz

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- VDD = 1.6 V to 5.5 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (66.6 μs: @ 15 kHz operation with low-speed on-chip oscillator clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- Address space: 1 Mbytes
- General-purpose registers: (8-bit register × 8) ×
 4 banks
- On-chip RAM: 1.5 Kbytes

Code flash memory

- Code flash memory: 16 Kbytes
- Block size: 1 Kbytes
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 2 Kbytes
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 48 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0% (VDD = 1.8 to 5.5 V, TA = -20 to +85°C)

Middle-speed on-chip oscillator

Selectable from 4 MHz, 2 MHz, and 1 MHz.

Operating ambient temperature

- TA = -40 to +85°C (A: Consumer applications)
- TA = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources.
- Chain transfer function

Event link controller (ELC)

 Event signals of 18 types can be linked to the specified peripheral function.

Serial interfaces

- Simplified SPI (CSI Note 1): 4 channels
- UART: 2 channels
- I²C/simplified I²C: 4 channels
- Multimaster I²C: 2 channels

RL78/G11

Timers

- 16-bit timer (TAU): 4 channels
- TKB: 1 channel
- 12-bit interval timer: 1 channel
- 8-bit interval timer: 2 channels
- Watchdog timer: 1 channel

A/D converter

- 8/10-bit resolution A/D converter (VDD = 1.6 to 5.5 V)
- Analog input: 10 to 11 channels
- Internal reference voltage (1.45 V) and temperature sensor

D/A converter

- 8/10-bit resolution D/A converter (VDD = 1.6 to 5.5 V)
- Analog input: 2 channels (channel 1: output to the ANO1 pin, channel 0: output to the comparator)
- Output voltage: 0 V to VDD
- Real-time output function

Comparator

- 2 channels
- Operating modes: Comparator high-speed mode, comparator low-speed mode, window mode

PGA

1 channels

I/O ports

- I/O port: 17 to 21 (N-ch open drain I/O [VDD withstand voltage^{Note 2}/EVDD withstand voltage^{Note 3}]: 10 to 14)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3.0 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller Others
- On-chip BCD (binary-coded decimal) correction circuit
- On-chip data operation circuit
- Note 1. Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.
- Note 2. 16, 20, 24-pin products
- Note 3. 25-pin products
- Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

○ ROM, RAM capacities

Flash	Data	RAM		RL78/G11					
ROM	flash	IN/NIVI	10 pins	16 pins	20 pins	24 pins	25 pins		
16 KB	2 KB	1.5 KB	R5F1051A	R5F1054A	R5F1056A	R5F1057A	R5F1058A		

Remark The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F105xA (x = 1, 4, 6, 7, 8): Start address FF900H

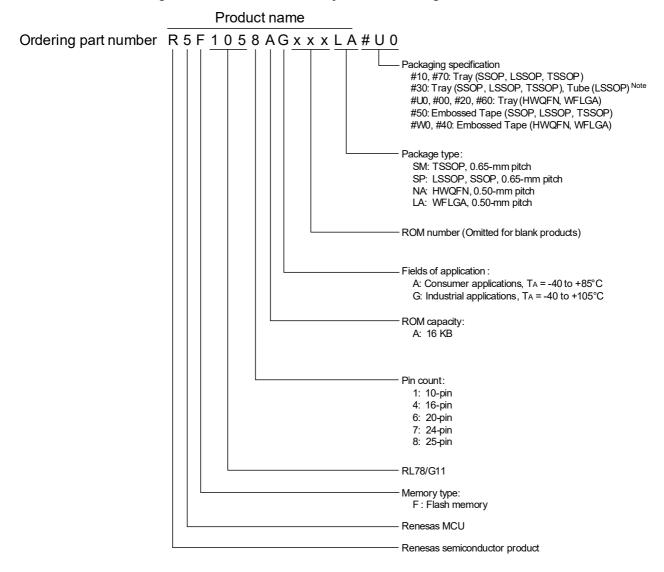
For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).



1.2 Ordering Information



Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11



Note The packaging specification is only "Tube" for products in the 20-pin LSSOP.



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	Pin		Ordering Part Numbe	r	
	Count	Package	Product Name	Packaging Specifications	RENESAS Code
	10 pins	10-pin plastic LSSOP	R5F1051AGSP, R5F1051AASP	#10, #30, #50,	PLSP0010JA-A
<r></r>		(4.4 × 3.6 mm, 0.65-mm pitch)		#70	
	16 pins	16-pin plastic SSOP	R5F1054AGSP, R5F1054AASP	#10, #30, #50,	PRSP0016JC-B
<r></r>		(4.4 × 5.0 mm, 0.65-mm pitch)		#70	
		16-pin plastic HWQFN	R5F1054AGNA, R5F1054AANA	#00, #20, #40,	PWQN0016KD-A
<r></r>		(3 × 3 mm, 0.50-mm pitch)		#60	PWQN0016KE-A
	20 pins	20-pin plastic LSSOP	R5F1056AGSP, R5F1056AASP	#30, #50	PLSP0020JB-A
		(4.4 × 6.5 mm, 0.65-mm pitch)			
		20-pin plastic TSSOP	R5F1056AGSM, R5F1056AASM	#10, #30, #50,	PTSP0020JI-A
<r></r>		(4.4 × 6.5 mm, 0.65-mm pitch)		#70	
	24 pins	24-pin plastic HWQFN	R5F1057AGNA, R5F1057AANA	#U0, #W0	PWQN0024KE-A
		$(4 \times 4 \text{ mm}, 0.50 \text{-mm pitch})$	R5F1057AGNA, R5F1057AANA	#00, #20, #40,	PWQN0024KF-A
<r></r>		(, , , , , , , , , , , , , , , , , , ,		#60	PWQN0024KH-A
	25 pins	25-pin plastic WFLGA	R5F1058AGLA, R5F1058AALA	#U0, #W0	PWLG0025KA-A
		(3 × 3 mm, 0.50-mm pitch)			

Table 1 - 1 List of Ordering Part Numbers	Table 1	- 1 List	of Ordering	Part	Numbers
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Caution 1. For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11.

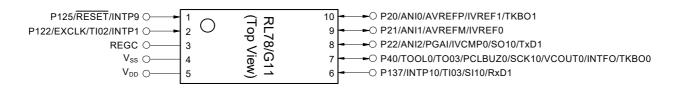
• The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Pin Configuration (Top View)

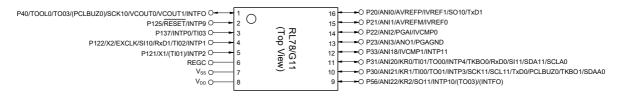
1.3.1 10-pin products

• 10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65-mm pitch)

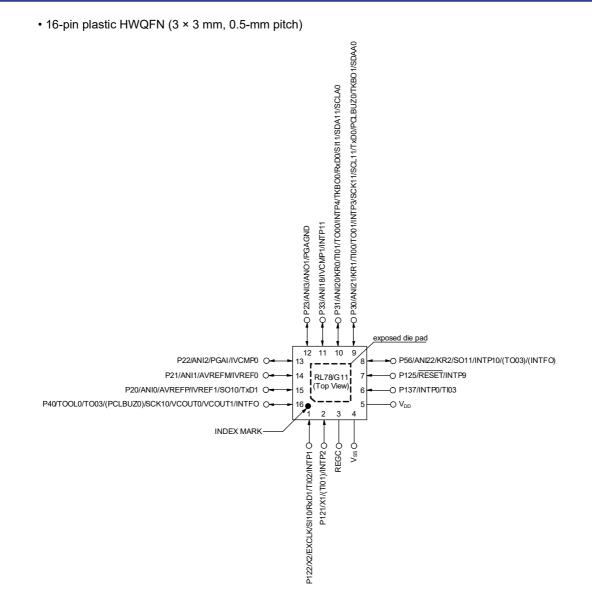


1.3.2 16-pin products

• 16-pin plastic SSOP (4.4 × 5.0 mm, 0.65-mm pitch)

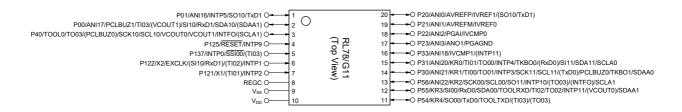






1.3.3 20-pin products

- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65-mm pitch)
- 20-pin plastic TSSOP (4.4 × 6.5 mm, 0.65-mm pitch)



Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

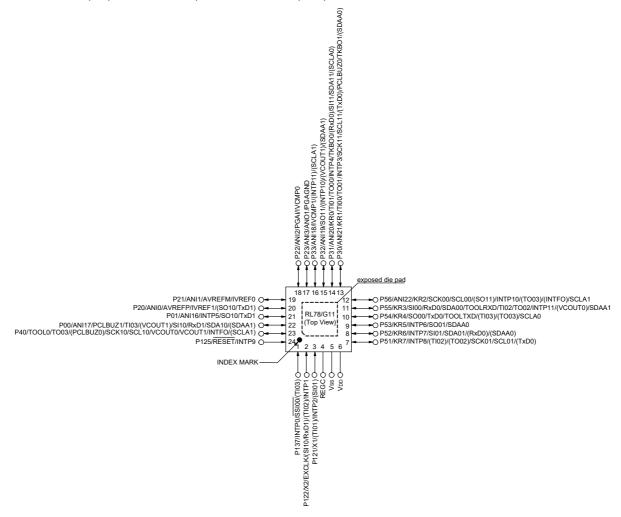
Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).



1.3.4 24-pin products

• 24-pin plastic HWQFN (4 × 4 mm, 0.5-mm pitch)



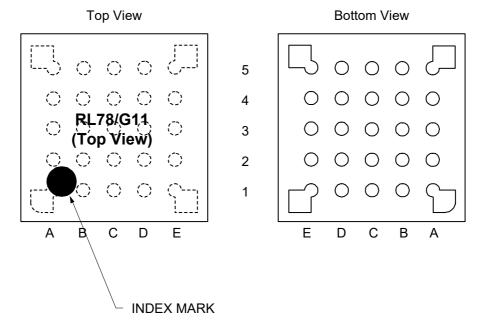
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. It is recommended to connect an exposed die pad to Vss.
- **Remark 3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).



1.3.5 25-pin products

• 25-pin plastic WFLGA (3 × 3 mm, 0.5-mm pitch)



	А	В	С	D	Е	
5	P40/TOOL0/TO03/(PC LBUZ0)/SCK10/SCL10 /VCOUT0/VCOUT1/IN TFO/(SCLA1)	P125/RESET/INTP9	P01/ANI16/INTP5/SO1 0/TxD1	P20/ANI0/AVREFP/IV REF1/(SO10/TxD1)	P21/ANI1/AVREFM/IV REF0	5
4	P122/X2/EXCLK/(SI10 /RxD1)/(TI02)/INTP1	P137/INTP0/SSI00/(TI 03)	P00/ANI17/PCLBUZ1/ TI03/(VCOUT1)/SI10/ RxD1/SDA10/(SDAA1)	P22/ANI2/PGAI/IVCM P0	P23/ANI3/ANO1/PGA GND	4
3	P121/X1/(TI01)/INTP2/ (SI01)	Vdd	EVDD	P33/ANI18/IVCMP1/(I NTP11)/(SCLA1)	P32/ANI19/SO11/(INT P10)/(VCOUT1)/(SDA A1)	3
2	REGC	Vss	P30/ANI21/KR1/TI00/T O01/INTP3/SCK11/SC L11/(TxD0)/PCLBUZ0/ TKBO1/(SDAA0)	P31/ANI20/KR0/TI01/T O00/INTP4/TKBO0/(R xD0)/SI11/SDA11/(SC LA0)	P56/ANI22/KR2/SCK0 0/SCL00/(SO11)/INTP 10/(TO03)/(INTFO)/SC LA1	2
1	P51/KR7/INTP8/(TI02) /(TO02)/SCK01/SCL01 /(TxD0)	P52/KR6/INTP7/SI01/ SDA01/(RxD0)/(SDAA 0)	P53/KR5/INTP6/SO01/ SDAA0	P54/KR4/SO00/TxD0/ TOOLTXD/(TI03)/(TO0 3)/SCLA0	P55/KR3/SI00/RxD0/S DA00/TOOLRXD/TI02/ TO02/INTP11/(VCOUT 0)/SDAA1	1
	А	В	С	D	E	

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).

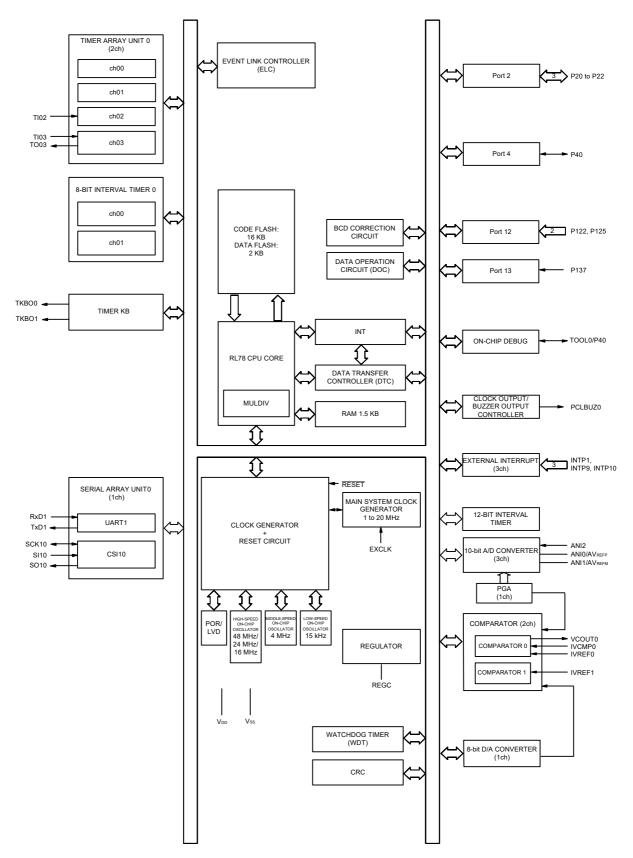
1.4 Pin Identification

ANI0 to ANI3,		PCLBUZ0, PCLBUZ1	: Programmable clock output/buzzer
ANI16 to ANI22	. Analag input	FOLDOZO, FOLDOZI	°
	: Analog input	BECC	output
ANO1	: Analog output	REGC	: Regulator capacitance
AVREFM	: A/D converter reference	RESET	: Reset
	potential (- side) input	RxD0, RxD1	: Receive data
AVREFP	: A/D converter reference	SCK00, SCK01,	
	potential (+ side) input	SCK10, SCK11	: Serial clock input/output
EVDD	: Power supply	SCLA0, SCLA1	: Serial clock input/output
EXCLK	: External clock input	SCL00, SCL01,	
	(main system clock)	SCL10, SCL11	: Serial clock output
INTP0 to INTP11	: External interrupt input	SDAA0, SDAA1	: Serial data input/output
INTFO	: Interrupt Flag output	SDA00, SDA01,	
IVCMP0, IVCMP1	: Comparator input	SDA10, SDA11	: Serial data input/output
IVREF0, IVREF1	: Comparator reference input	SI00, SI01,	
KR0 to KR7	: Key return	SI10, SI11	: Serial data input
PGAI, PGAGND	: PGA Input	SO00, SO01,	
P00 to P01	: Port 0	SO10, SO11	: Serial data output
P20 to P23	: Port 2	<u>SSI00</u>	: Serial interface chip select input
P30 to P33	: Port 3	TI00 to TI03	: Timer input
P40	: Port 4	TKBO0, TKBO1	: TMKB output
P51 to P56	: Port 5	TO00 to TO03	: Timer output
P121, P122, P125	: Port 12	TOOL0	: Data input/output for tool
P137	: Port 13	TOOLRXD, TOOLTXD	: Data input/output for external device
		TxD0, TxD1	: Transmit data
		VCOUT0, VCOUT1	: Comparator output
		Vdd	: Power supply
		Vss	: Ground
		X1, X2	: Crystal oscillator (main system clock)



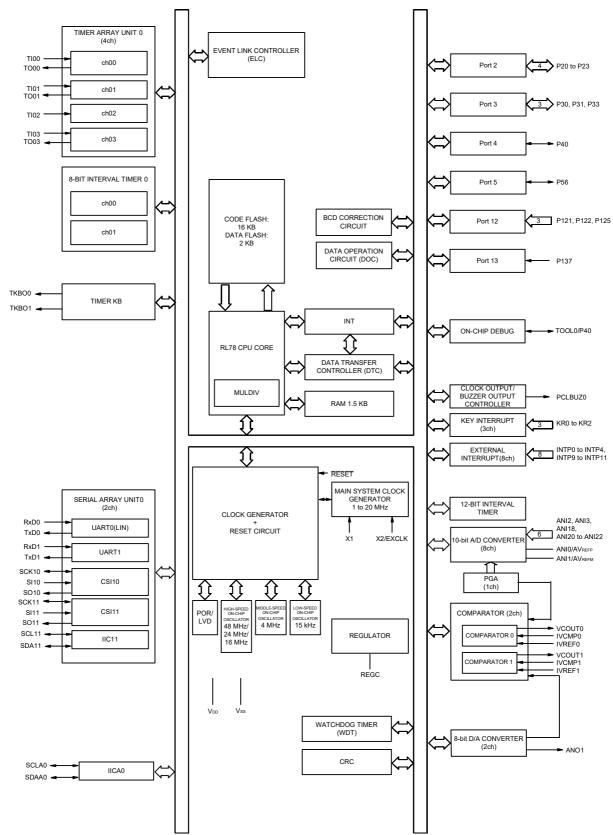
1.5 Block Diagram

1.5.1 10-pin products



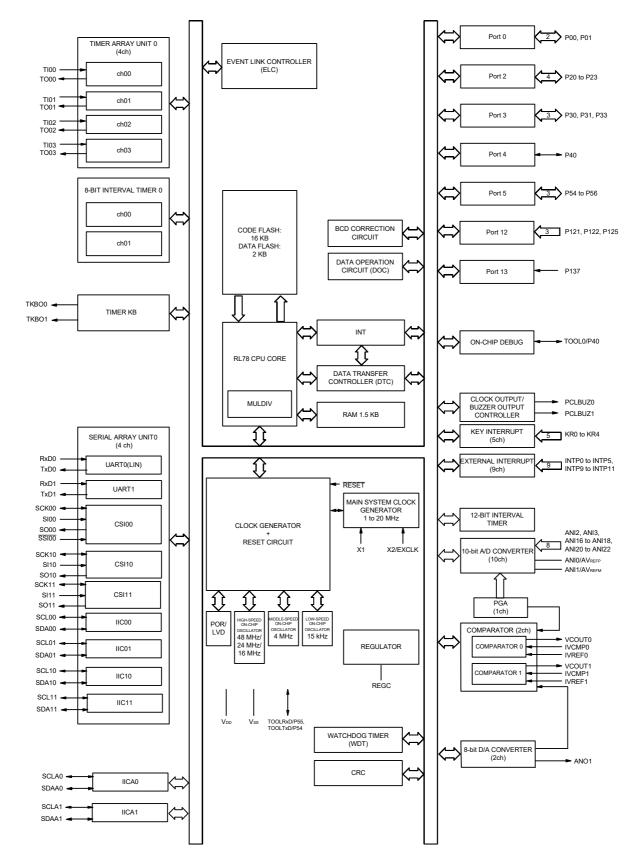


1.5.2 16-pin products



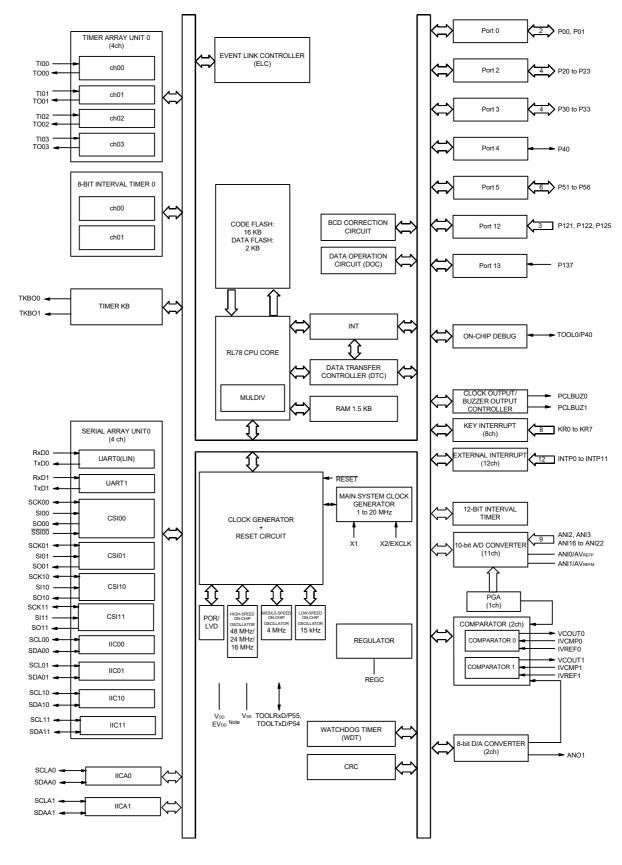


1.5.3 20-pin products





1.5.4 24-pin, 25-pin products



Note 25-pin products



1.6 Outline of Functions

This outline describes the functions at the time when Peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3) are set to 00H.

361 10 01						(1/2				
	ltem	10-pin	16-pin	20-pin	24-pin	25-pin				
	Item	R5F1051A	R5F1054A	R5F1056A	R5F1057A	R5F1058A				
Code flash r	nemory (KB)		L	16 Kbytes						
Data flash m	nemory (KB)		2 Kbytes							
RAM			1.5 Kbytes							
Address spa	ice	1 Mbytes								
Main	High-speed system	X1 (crystal/ceramic) o	scillation ^{Note} , external r	nain system clock inpu	t (EXCLK)					
system	clock (fmx)	1 to 20 MHz: VDD = 2.	7 to 5.5 V							
clock		1 to 16 MHz: VDD = 2.	to 16 MHz: Vdd = 2.4 to 5.5 V							
		1 to 8 MHz: VDD = 1.8	to 5.5 V							
		1 to 4 MHz: VDD = 1.6	to 4 MHz: V _{DD} = 1.6 to 5.5 V							
	High-speed on-chip	HS (High-speed main) mode: 1 to 24 MHz (VDD = 2.7 to 5.5 V),								
	oscillator clock (fiH)	HS (High-speed main	IS (High-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V),							
	Max: 24 MHz	LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V),								
	Middle-speed on-	LV (Low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V),								
	chip oscillator clock	LP (Low-power main)	mode: 1 MHz (VDD =	1.8 to 5.5 V)						
	(fim) Max: 4 MHz									
Subsystem	Low-speed on-chip	15 kHz (typ.): VDD = 1	5 kHz (typ.): VDD = 1.6 to 5.5 V							
clock	oscillator clock (fiL)									
General-pur	pose register	8 bits \times 32 registers (8	3 bits $ imes$ 8 registers $ imes$ 4 b	oanks)						
Minimum ins	struction execution	0.04167 μ s (High-speed on-chip oscillator clock: fi μ = 24 MHz operation)								
time		0.05 μs (High-speed system clock: fмx = 20 MHz operation)								
Instruction s	et	Data transfer (8/16 I	oits)							
		Adder and subtractor/logical operation (8/16 bits)								
		• Multiplication (8 bits \times 8 bits, 16 bits \times 16 bits), Division (16 bits \div 16 bits, 32 bits \div 32 bits)								
			ccumulation (16 bits \times 1	,						
			and bit manipulation (S		1 2					
I/O port	Total	7	13	17		.1				
	CMOS I/O	4	9	13	1	7				
	CMOS input	3		4	4					
Timer	16-bit timer	4 channels								
	Watchdog timer	1 channel								
	Timer KB	1 channel								
	12-bit interval timer	1 channel								
	8/16-bit interval timer	2 channels (8 bit)/1 ch	nannel (16 bit)							
	Timer output	3	5		6					
	1	1	1							

Note 16, 20, 24, 25-pin products

Caution The flash library uses RAM in self-programming and rewriting of the data flash memory. The target products and start address of the RAM areas used by the flash library are shown below.

R5F105xA (x = 1, 4, 6, 7, 8): Start address FF900H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).



(2/2)

						(2/2		
Iten		10-pin	16-pin	20-pin	24-pin	25-pin		
	·	R5F1051A	R5F1054A	R5F1056A	R5F1057A	R5F1058A		
Clock output/b	uzzer		1		24-pin 25-pin R5F1057A R5F1058A 2 11 channels nnels			
output		(Main system clock: f			Note Note <th< td=""></th<>			
10-bit	External	3 channels	8 channels	10 channels	11 cha	annels		
resolution A/D converter	Internal	1 channel		<u> </u>	<u> </u>			
8-bit D/A conv	erter	1 channel		2 cha	innels			
Comparator (V Comparator)	Vindow	1 channel		2 cha	2 channels			
PGA		1 channel						
Data Operation (DOC)	n Circuit	Comparison, addition, a	nd subtraction of 16-bit o	lata				
Serial interface	3	 [16-pin products] Simplified SPI (CSI): 2 [20-pin products] Simplified SPI (CSI): 3 [24-pin, 25-pin products] 	 Simplified SPI (CSI): 1 channel/UART: 1 channel [16-pin products] Simplified SPI (CSI): 2 channels/UART: 2 channels/simplified I²C: 1 channel 					
	I ² C bus	None 1 channel 2 channels						
Data transfer o (DTC)	controller	13 sources	22 sources	23 sources	24 sources			
Event link cont (ELC)	troller	Event input: 11 Event trigger output: 3	Event input: 16 Event trigger output: 4	Event input: 17 Event trigger output: 4	•			
Vectored	Internal	20	24		25			
interrupt sources	External	3	9	10	1	3		
Key interrupt		None	3	5	8	3		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Internal reset by RAM parity error Internal reset by illegal-memory access						
Power-on-rese	et circuit	1.51 • Power-down-reset: 1.5	± 0.04V (TA = -40 to +85 ± 0.06V (TA = +85 to +10 50 ± 0.04 V (TA = -40 to - 50 ± 0.06V (TA = +85 to +)5°C) ⊦85°C)				
Voltage	ge Power on 1.67 V to 4.06 V (14 stages)							
detector	Power down	1.63 V to 3.98 V (14 sta	ges)					
On-chip debug	g function	Provided (Disable to tra	cing)					
Power supply	voltage	V _{DD} = 1.6 to 5.5 V						
Operating amb temperature	pient	T _A = -40 to +85°C (Cons T _A = -40 to +105°C (Ind						



2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

- Target products A: Consumer applications (TA = -40 to $+85^{\circ}$ C)
 - R5F105xxAxx
 - G: When the products "G: Industrial applications (TA = -40 to $+105^{\circ}$ C)" is used in the range of TA = -40 to $+85^{\circ}$ C R5F105xxGxx
- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G11 User's Manual.
 - Caution 3. The EVDD pin is not present on products with 24 or less pins. Accordingly, replace EVDD with VDD and the voltage condition $1.6 \le EVDD \le VDD \le 5.5$ V with $1.6 \le VDD \le 5.5$ V.



(4.0)

2.1 Absolute Maximum Ratings

				(1/2)
Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD		-0.5 to +6.5	V
	AVREFP		0.3 to VDD + 0.3 Note 2	V
	AVREFM		-0.3 to VDD + 0.3 Note 2	V
			and AVREFM \leq AVREFP	
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to VDD + 0.3 ^{Note 1}	
Input voltage	VI1	P00, P01, P30 to P33, P40, and P51 to	-0.3 to EVDD + 0.3	V
		P56	and -0.3 to VDD + 0.3 Note 2	
	VI2	P20 to P23, P121, P122, P125, P137,	-0.3 to VDD + 0.3 Note 2	V
		EXCLK, RESET		
Output voltage	V01	P00, P01, P30 to P33, P40, and P51 to	-0.3 to EVDD + 0.3	V
		P56	and -0.3 to VDD + 0.3 Note 2	
	Vo2	P20 to P23	-0.3 to VDD + 0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI22	-0.3 to EVDD + 0.3	V
			and -0.3 to AVREF(+) + 0.3 Notes2,3	
	VAI2	ANI0 to ANI3	-0.3 to VDD + 0.3	V
			and -0.3 to AVREF(+) + 0.3 Notes 2, 3	

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. AVREF (+): + side reference voltage of the A/D converter.

Remark 3. Vss: Reference voltage



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Parameter	Symbols		Conditions	Ratings	Unit	
Output current, high	Іон1	Per pin		-40	mA	
	t current, high $Per pin$ Total of all pins -170 mA $P00, P01, P40$ -170 mA $P30 to P33, P51 to P56P00, P01, P40P30 to P33, P51 to P56P20 to P23Per pin$ $P20 to P23Per pin$ $P00, P01, P40Pan P20 to P23Pan P20 to P23Pan P20 to P23Pan P20 to P33, P51 to P56Pan P20 to P33, P51 to P56Pan P20 to P23Pan P2$	P00, P01, P40	-70	mA		
		Per pinP00, P01, P40Total of all pins -170 mAP30 to P33, P51 to P56Per pinP20 to P23Total of all pinsP00, P01, P40Per pinP00, P01, P40170 mAP30 to P33, P51 to P56Per pinP20 to P23Total of all pinsP20 to P23In normal operation modeIn flash memory programming mode	-100	mA		
	Іон2	Per pin	P20 to P23	-0.5	mA	
			-2	mA		
Output current, low	IOL1	Per pin		40	mA	
	-			Total of all pins	P00, P01, P40	70
		170 mA	P30 to P33, P51 to P56	100	mA	
	IOL2	Per pin	P20 to P23	1	mA	
		Total of all pins		4	mA	
Operating ambient	ТА	In normal operat	ion mode	-40 to +85	°C	
temperature		In flash memory	programming mode	1		
Storage temperature	Tstg			-65 to +150	°C	

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



2.2 Oscillator Characteristics

2.2.1 X1 characteristics

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 5.5 V, Vss = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~\text{V} \leq \text{V}\text{DD} < 2.7~\text{V}$	1.0		16.0	
		$1.8 \text{ V} \leq \text{Vdd} < 2.4 \text{ V}$	1.0		8.0	
		$1.6~V \le V \text{dd} < 1.8~V$	1.0		4.0	

Note Indicates only permissible oscillator frequency ranges. Refer to 2.4 AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Remark When using the X1 oscillator, refer to 6.4 System Clock Oscillator in the RL78/G11 User's Manual.

2.2.2 On-chip oscillator characteristics

(TA = -40 to +85°C, 1.6 V \leq VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1		24	MHz
		$2.4~V \leq V_{DD} \leq$	5.5 V	1		16	
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	1		8	
		$1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	1		4	
High-speed on-chip oscillator clock frequency accuracy		TA = -20 to	$1.8~V \le V_{DD} \le 5.5~V$	-1		1	%
	+85°C	$1.6~V \leq V_{DD} < 1.8~V$	-5		5		
		TA = -40 to	$1.8~V \le V_{DD} \le 5.5~V$	-1.5		1.5	%
		-20°C	$1.6~V \leq V_{DD} < 1.8~V$	-5.5		5.5	
Middle-speed on-chip oscillator oscillation frequency Note 2	fıм		·	1		4	MHz
Middle-speed on-chip oscillator oscillation frequency accuracy				-12		+12	%
Temperature drift of Middle-speed on-chip oscillator oscillation frequency accuracy	DIMT				0.008		%/°C
Voltage drift of Middle-speed on-chip oscillator oscillation	DIMV	TA = 25°C	$2.1~V \leq V_{DD} \leq 5.5~V$		0.02		%/V
frequency accuracy			$2.0~V \leq V_{DD} < 2.1~V$		-12		
			$1.6~\text{V} \leq \text{V}_\text{DD} < 2.0~\text{V}$		10		
Low-speed on-chip oscillator clock frequency Note 2	fı∟		1		15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to 2.4 AC Characteristics for instruction execution time.



Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

2.3 **DC Characteristics**

Pin characteristics 2.3.1

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(TA = -40 to +85°C,	1.6 V ≤ E	$VDD \leq VDD \leq 5.5 V$, $Vss = 0 V$)					(1/5)	
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit	
Output current, high Note 1	Іон1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				-10.0 Note 2	mA	
		Total of P00, P01, and P40	$4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$			-42.0	mA	
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			-10.0	mA	
			$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			-5.0	mA	
			$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			-2.5	mA	
		Total of P30 to P33, and P51 to P56	$4.0~V \le EV_{DD} \le 5.5~V$			-80.0	mA	
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			-19.0	mA	
		(When duty ≤ 70% ^{Note 3})	$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			-10.0	mA	
			$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			-5.0	mA	
		Total of all pins (When duty ≤ 70% ^{Note 3})				-122.0	mA	
	Іон2	Per pin for P20 to P23				-0.1 Note 2	mA	
		Total of all pins (When duty ≤ 70% ^{Note 3})	$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			-0.4	mA	

Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin. Note 1.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IOH × 0.7)/(n × 0.01)

<Example> Where n = 80% and IOH = -10.0 mA Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				20.0 Note 2	mA
		Total of P00, P01, and P40	$4.0~V \leq EV_{DD} \leq 5.5~V$			70.0	mA
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$			15.0	mA
			$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			9.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			4.5	mA
		Total of P30 to P33, and P51 to P56	$4.0~V \leq EV_{DD} \leq 5.5~V$			80.0	mA
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$			35.0	mA
			$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			20.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				150.0	mA
	IOL2	Per pin for P20 to P23				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$			1.6	mA

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

 Total output current of pins = (IoL × 0.7)/(n × 0.01)
 <Example> Where n = 80% and IoL = 10.0 mA Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≈ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0.8 EVDD		EVDD	V
	VIH2	P00, P30 to P32, P40, P51 to P56	TTL mode 4.0 V \leq EV _{DD} \leq 5.5 V	2.2		EVdd	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	2.0		EVDD	V
		TTL mode 1.6 V ≤ EV _{DD} < 3.3		1.5		EVDD	V
	Vінз	P20 to P23 (digital input)		0.7 Vdd		Vdd	V
	VIH4	P121, P122, P125, P137, EXCL	0.8 Vdd		Vdd	V	
Input voltage, low	VIL1	P00, P01, P30 to P33, P40, and P51 to P56				0.2 EVDD	V
	VIL2	P00, P30 to P32, P40, P51 to P56	TTL mode $4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$	0		0.8	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	0		0.5	V
			TTL mode 1.6 V ≤ EV _{DD} < 3.3 V	0		0.32	V
	Vінз	P20 to P23 (digital input)	1	0		0.3 Vdd	V
	VIH4	P121, P122, P125, P137, EXCL		0		0.2 VDD	V

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{FV}$ DD $\le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

The maximum value of VIH of pins P00, P01, P20, P30 to P33, P40 and P51 to P56 is VDD or EVDD, even in the N-ch Caution open-drain mode.

(P20: VDD

P00, P01, P30 to P33, P40, P51 to P56: EVDD)



Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark

Items	Symbol	Conc	itions	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00, P01, P30 to P33, P40, and P51 to P56	4.0 V ≤ EVDD ≤ 5.5 V, Іон = -10.0 mA	EVDD - 1.5			V
			4.0 V ≤ EVDD ≤ 5.5 V, Іон = -3.0 mA	EVDD - 0.7			V
			2.7 V ≤ EVDD ≤ 5.5 V, Іон = -2.0 mA	EVDD - 0.6			V
			1.8 V ≤ EVDD ≤ 5.5 V Іон = -1.5 mA	EVDD - 0.5			V
			1.6 V ≤ EVDD ≤ 5.5 V, Іон = -1.0 mA	EVDD - 0.5			V
	Voh2	P20 to P23	1.6 V ≤ Vdd ≤ 5.5 V, Іон = -100 µА	Vdd - 0.5			V
Output voltage, low	VOL1	P00, P01, P30 to P33, P40, and P51 to P56	$4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ IOL = 20.0 mA			1.3	V
			$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ $\text{IOL} = 8.5 \text{ mA}$			0.7	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ IOL = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ IOL = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ IOL = 0.6 mA			0.4	V
			$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ IOL = 0.3 mA			0.4	V
	Vol2	P20 to P23	$1.6 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ Iol = 400 µA			0.4	V

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

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P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode. Caution

Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark



(IA = -40 to +8	5°C, 1.6 V	$V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0$	V)		-			(5/5)
Items	Symbol	Conc	litions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00, P01, P30 to P33, P40, and P51 to P56	VI = EVDD				1	μA
	ILIH2	P20 to P23, P125, P137, RESET	VI = VDD				1	μA
	Ілнз	P121, P122, X1, X2, EXCLK	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	ILIL1	P00, P01, P30 to P33, P40, and P51 to P56	VI = Vss				-1	μA
	ILIL2	P20 to P23, P125, P137, RESET	VI = Vss				-1	μA
	Ilil3	P121, P122, X1, X2, EXCLK	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P00, P01, P30 to P33, P40, P51 to P56, P125	Vı = Vss, lı	n input port	10	20	100	kΩ

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark



Supply current characteristics 2.3.2

($(T_A = -40 \text{ to } +85^{\circ}\text{C}.)$	1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)
	17		,

Parameter	Symbol				Conditions			MIN.	TYP.	MAX.	Unit
Supply current	IDD1	Operating	Basic	HS (high-speed main)	fHOCO = 48 MHzNote 3	V _{DD} = 5.0 V			1.7		mA
ote 1		mode	operation	mode	fiH = 24 MHz Note 3	V _{DD} = 3.0 V			1.7		
					fHOCO = 24 MHzNote 3	V _{DD} = 5.0 V			1.4		
					fiH = 24 MHz Note 3	V _{DD} = 3.0 V			1.4		
			Normal	HS (high-speed main)	fHOCO = 48 MHz ^{Note 3}	V _{DD} = 5.0 V			3.5	6.9	mA
			operation	mode	f _{IH} = 24 MHz ^{Note 3}	V _{DD} = 3.0 V			3.5	6.9	
					fHOCO = 24 MHzNote 3	V _{DD} = 5.0 V			3.2	6.3	
					fiH = 24 MHz Note 3	V _{DD} = 3.0 V			3.2	6.3	
					fHOCO = 16 MHzNote 3	V _{DD} = 5.0 V			2.4	4.6	
					fiH = 16 MHz Note 3	V _{DD} = 3.0 V			2.4	4.6	1
			Normal	LS (low-speed main)	fiH = 8 MHz Note 3	V _{DD} = 3.0 V			1.1	2.0	mA
			operation	mode (MCSEL = 0)		V _{DD} = 2.0 V			1.1	2.0	
			Normal	LS (low-speed main)	fiH = 4 MHz Note 3	V _{DD} = 3.0 V			0.72	1.3	mA
			operation	mode (MCSEL = 1)		V _{DD} = 2.0 V			0.72	1.3	
				(MOSEL = 1)	fim = 4 MHz Note 6	V _{DD} = 3.0 V			0.58	1.1	1
						V _{DD} = 2.0 V			0.58	1.1	
			Normal	LV (low-voltage main)	fiH = 4 MHz Note 3	V _{DD} = 3.0 V			1.2	1.8	m/
			operation	mode		V _{DD} = 2.0 V			1.2	1.8	
			Normal	LP (low-power main)	fiH = 1 MHz Note 3	V _{DD} = 3.0 V			290	480	μA
			operation	mode (MCSEL = 1)		V _{DD} = 2.0 V			290	480	
					fim = 1 MHz Note 6	V _{DD} = 3.0 V			124	230	
						V _{DD} = 2.0 V			124	230	
			Normal	HS (high-speed main)	f_{MX} = 20 MHz Note 2	V _{DD} = 5.0 V	Square wave input		2.7	5.3	m/
			operation	mode			Resonator connection		2.8	5.5	
						V _{DD} = 3.0 V	Square wave input		2.7	5.3	
							Resonator connection		2.8	5.5	
					f_{MX} = 10 MHz Note 2	V _{DD} = 5.0 V	Square wave input		1.8	3.1	
							Resonator connection		1.9	3.2	
						V _{DD} = 3.0 V	Square wave input		1.8	3.1	
							Resonator connection		1.9	3.2	
			Normal	LS (low-speed main)	f _{MX} = 8 MHz Note 2	V _{DD} = 3.0 V	Square wave input		0.9	1.9	m
			operation	mode (MCSEL = 0)			Resonator connection		1.0	2.0	
			Normal		f _{MX} = 8 MHz ^{Note 2}	V _{DD} = 2.0 V	Square wave input		0.9	1.9	
			operation				Resonator connection		1.0	2.0	
			Normal	LS (low-speed main)	f _{MX} = 4 MHz ^{Note 2}	V _{DD} = 3.0 V	Square wave input		0.6	1.1	m
			operation	mode			Resonator connection		0.6	1.2	
			Normal	(MCSEL = 1)	f _{MX} = 4 MHz Note 2	V _{DD} = 2.0 V	Square wave input		0.6	1.1	
			operation				Resonator connection		0.6	1.2	
			Normal	LP (low-power main)	f _{MX} = 1 MHz ^{Note 2}	V _{DD} = 3.0 V	Square wave input		100	190	μA
			operation	mode (MCSEL = 1)			Resonator connection		145	250	
			Normal	、 ·/	f _{MX} = 1 MHz Note 2	V _{DD} = 2.0 V	Square wave input		100	190]
			operation				Resonator connection	1	145	250	1

(Notes and Remarks are listed on the next page.)



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(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

										. ,
Parameter	Symbol				Conditions		MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD1	Operating mode	Normal operation	clock	f_{IL} = 15 kHz, T_A = -40°C Note 5	Normal operation		1.8	5.9	μA
				operation	fiL = 15 kHz, T _A = +25°C Note 5	Normal operation		1.9	5.9	
					fiL = 15 kHz, T _A = +85°C Note 5	Normal operation		2.3	8.7	

Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main), LS (low-speed main), LV (low-voltage main), and LP (low-power main) modes.

- The currents in the "TYP." column do not include the operating currents of the peripheral modules.
- The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- Note 3. When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- Note 4. When the high-speed system clock is stopped.
- Note 5. When the high-speed system clock, high-speed on-chip oscillator clock and middle-speed on-chip oscillator clock are stopped.
- Note 6. When the high-speed system clock, high-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. fill: High-speed on-chip oscillator clock frequency (24 MHz max.)

- Remark 3. fim: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fiL: Low-speed on-chip oscillator clock frequency
- **Remark 5.** fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)
- Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



Deveryort	0	1		0			MINI	T)/D	MANY	(3/4
Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT	HS (high-speed main) mode	fHOCO = 48 MHz ^{Note 4}	VDD = 5.0 V			0.59	2.43	mA
lote 1	Note 2	mode		fin = 24 MHz Note 4	VDD = 3.0 V			0.59	2.43	
				fHOCO = 24 MHz ^{Note 4}	V _{DD} = 5.0 V			0.41	1.83	
				fin = 24 MHz Note 4	VDD = 3.0 V			0.41	1.83	
				fHOCO = 16 MHzNote 4	VDD = 5.0 V			0.39	1.38	
				fiH = 16 MHz Note 4,	V _{DD} = 3.0 V			0.39	1.38	
			LS (low-speed main) mode	fiH = 8 MHz Note 4	V _{DD} = 3.0 V			250	710	μA
			(MCSEL = 0)		VDD = 2.0 V			250	710	
			LS (low-speed main) mode	fiH = 4 MHz Note 4	V _{DD} = 3.0 V			204	400	μA
			(MCSEL = 1)		V _{DD} = 2.0 V			204	400	
				fim = 4 MHz Note 6	VDD = 3.0 V			43	250	
					V _{DD} = 2.0 V			43	250	
			LV (low-voltage main) mode	fiH = 4 MHz Note 4	V _{DD} = 3.0 V			450	700	μA
					V _{DD} = 2.0 V			450	700	
			LP (low-power main) mode	fiH = 1 MHz Note 4	V _{DD} = 3.0 V			192	400	μA
			(MCSEL = 1)		V _{DD} = 2.0 V			192	400	
				fim = 1 MHz Note 6	V _{DD} = 3.0 V			28	100	
					V _{DD} = 2.0 V			28	100	
			HS (high-speed main) mode	f _{MX} = 20 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.20	1.55	mA
						Resonator connection		0.40	1.74	
					V _{DD} = 3.0 V	Square wave input		0.20	1.55	
						Resonator connection		0.40	1.74	
				f _{MX} = 10 MHz Note 3	VDD = 5.0 V	Square wave input		0.15	0.86	
						Resonator connection		0.30	0.93	
					V _{DD} = 3.0 V	Square wave input		0.15	0.86	
						Resonator connection		0.30	0.93	
			LS (low-speed main) mode	f _{MX} = 8 MHz Note 3	V _{DD} = 3.0 V	Square wave input		68	550	μA
			(MCSEL = 0)			Resonator connection		125	590	
				f _{MX} = 8 MHz Note 3	VDD = 2.0 V	Square wave input		68	550	
						Resonator connection		125	590	
			LS (low-speed main) mode	f _{MX} = 4 MHz Note 3	V _{DD} = 3.0 V	Square wave input		23	128	μA
			(MCSEL = 1)			Resonator connection		65	200	
				f _{MX} = 1 MHz Note 3	V _{DD} = 2.0 V	Square wave input		23	128	
						Resonator connection		65	200	
			LP (low-power main) mode	f _{MX} = 4 MHz Note 3	V _{DD} = 3.0 V	Square wave input		10	64	μA
			(MCSEL = 1)			Resonator connection		59	150	
	1	1		f _{MX} = 1 MHz Note 3	V _{DD} = 2.0 V	Square wave input		10	64	
	1	1				Resonator connection		59	150	
	1	1	Subsystem clock operation	fı∟ = 15 kHz, T₄= -40°C	Note 5			0.48	1.22	μA
	1	1		fi∟ = 15 kHz, T _A = +25°0				0.55	1.22	
	1			fi∟ = 15 kHz, T _A = +85°C				0.80	3.30	

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(3/4)

(Notes and $\ensuremath{\textit{Remarks}}$ are listed on the next page.)



- Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main), LS (low-speed main), LV (low-voltage main), and LP (low-power main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. When the HALT instruction is executed in the flash memory.
- Note 3. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and low-speed on-chip oscillator clock are stopped.
- **Note 4.** When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 5.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and high-speed system clock are stopped.
- Note 6. When the high-speed system clock, high-speed on-chip oscillator clock, and low-speed on-chip oscillator clock are stopped.
- **Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fill: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 3. fim: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fiL: Low-speed on-chip oscillator clock frequency
- Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)
- Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



(4/4)

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

-			-				
Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Supply current	IDD3	STOP mode	TA = -40°C		0.19	0.51	μA
Note 1		Note 2	TA = +25°C		0.25	0.51	1
			TA = +50°C		0.28	1.10	1
			TA = +70°C		0.38	1.90	1
			TA = +85°C		0.60	3.30	1

Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

Note 2. For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when operating the subsystem clock in HALT mode.



Peripheral Functions (Common to all products)

(TA = -40 to +85°C, 1.6 V \leq EVDD $\leq~$ VDD $\leq~$ 5.5 V, Vss = 0 V)

	1			T	1	1	-
Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.22		μA
12-bit interval timer operating current	I _{TMKA} Notes 1, 3, 4	fiL = 15 kHz fmain stopped (per unit)			0.02		μΑ
8-bit interval timer operating current	Ітмт	fı∟ = 15 kHz	8-bit counter mode × 2-channel operation		0.04		μA
Notes 1, 9		fmain stopped (per unit)	16-bit counter mode operation		0.03		μA
Watchdog timer operating current	I _{WDT} Notes 1, 3, 5	fiL = 15 kHz fmain stopped (per unit)			0.22		μA
A/D converter operating current	ADC Notes 1, 6	During maximum-speed	Normal mode, AV _{VREFP} = V_{DD} = 5.0 V		1.3	1.7	mA
		conversion	Low voltage mode, AV _{VREFP} = V_{DD} = 3.0 V		0.5	0.7	mA
Internal reference voltage (1.45 V) current Notes 1, 10	Iadref				85.0		μΑ
Temperature sensor operating current	ITMPS Note 1				85.0		μA
D/A converter operating current	IDAC Notes 1, 14	Per channel				1.5	mA
PGA operating current	IPGA Notes 1, 2				480	700	μA
Comparator operating current	ICMP Note 8	V _{DD} = 5.0 V, Regulator output voltage	Comparator high-speed mode Window mode		12.5		μΑ
		= 2.1 V	Comparator low-speed mode Window mode		3.0		
			Comparator high-speed mode Standard mode		6.5		
			Comparator low-speed mode Standard mode		1.9		
		V _{DD} = 5.0 V, Regulator output voltage	Comparator high-speed mode Window mode		8.0		
		= 1.8 V	Comparator low-speed mode Window mode		2.2		
			Comparator high-speed mode Standard mode		4.0		
			Comparator low-speed mode Standard mode		1.3		
LVD operating current	ILVD Notes 1, 7				0.10		μA
Self-programming operating current	IFSP Notes 1, 12				2.0	12.20	mA
BGO current	IBGO Notes 1, 11				2.0	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	Mode transition Note 13		0.50	0.60	mA
		fih = 24 MHz, AVREFP = VDD = 3.0 V	The A/D conversion operations are performed		1.20	1.44	mA
		Simplified SPI (CSI)/UART	operation fiн = 24 MHz		0.70	0.84	mA
	ISNOZM Note 1	ADC operation	Mode transition Note 13		0.05	0.08	mA
		fim = 4 MHz, AVREFP = VDD = 3.0 V	The A/D conversion operations are performed		0.67	0.78	mA
		Simplified SPI (CSI) operate	tion, fim = 4 MHz		0.06	0.08	mA

(Notes and Remarks are listed on the next page.)



Note 1. Current flowing to VDD.

- Note 2. Operable range is 2.7 to 5.5 V.
- **Note 3.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and high-speed system clock are stopped.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- **Note 8.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 9. Current flowing only to the 8-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 8-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 10. Current consumed by generating the internal reference voltage (1.45 V).
- Note 11. Current flowing during programming of the data flash.
- Note 12. Current flowing during self-programming.
- Note 13. For transition time to the SNOOZE mode, see 24.3.3 SNOOZE mode in the RL78/G11 User's Manual.
- **Note 14.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fcLK: CPU/peripheral hardware clock frequency
- **Remark 3.** Temperature condition of the TYP. value is $TA = 25^{\circ}C$



2.4 **AC Characteristics**

$TA = -40 \text{ to } +85^{\circ}C,$	1.6 V ≤ E	$VDD \leq VDD \leq 5.5$	/, Vss = 0 V)					(1/2)
Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Тсү	Main system clock	HS (high-speed main)	$2.7~V \leq V \text{DD} \leq 5.5~V$	0.04167		1	μs
(minimum instruction		(fmain) operation	mode	$2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V}$	0.0625		1	μs
execution time)			LS (low-speed main) mode	$1.8 V \le VDD \le 5.5 V$ PMMC. MCSEL = 0	0.125		1	μs
				1.8 V ≤ VDD ≤ 5.5 V PMMC. MCSEL = 1	0.25		1	
			LP (low-power main) mode	$1.8 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$		1		μs
			LV (low-voltage main) mode	$1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	0.25		1	μs
		Subsystem clock (fsub) operation	fiL	$1.8 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$		66.7		μs
		In the self-	HS (high-speed main)	$2.7~V \leq V\text{DD} \leq 5.5~V$	0.04167		1	μs
		programming	mode	$2.4 \text{ V} \le \text{VDD} \le 2.7 \text{ V}$	0.0625		1	μs
		mode	LS (low-speed main) mode	$1.8 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-voltage main) mode	$1.8 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.25		1	μs
External system	fEX	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	/		1		20	MHz
clock frequency		$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}_{\text{DD}}$	/		1		16	MHz
		$1.8 V \le V_{DD} < 2.4 V_{DD}$	1		1		8	MHz
		$1.6 V \le V_{DD} < 1.8 V_{DD}$	1		1		4	MHz
External system	texн,	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}_{\text{DD}}$	1		24			ns
clock input high-/low- t level width	t EXL	$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			30			ns
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}_{\text{DD}}$	/		60			ns
		$1.6 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$			120			ns
TI00 to TI03 input high-/low-level width	ttih, ttil ^{Note}				1/fмск + 10			ns

Note Following conditions must be satisfied on low level interface of EVDD < VDD. $1.8~V \leq EV_{DD} \leq 2.7~V:$ MIN. 125 ns $1.6 \text{ V} \leq \text{EV}_{\text{DD}} < 1.8 \text{ V}$: MIN. 250 ns

Remark fмск: Timer array unit operation clock frequency (Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))



Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
TO00 to TO03, TKBO0, and TKBO1 output frequency Note	fro	TO00 to TO03, TKBO0, and TKBO1 (in the case of output from port pins other than P20)	HS (high-speed main) mode	$4.0~V \le EV_{DD} \le 5.5~V$	12	12	MHz	
				$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			8	
				$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			4	
				$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			2	
			LS (low-speed main) mode	$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$			4	
				1.6 V ≤ EVDD < 1.8 V			2	
			LP (low-power main) mode	$1.8 \text{ V} \le \text{EV}\text{DD} \le 5.5 \text{ V}$			0.5	
			LV (low-voltage main) mode	$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$			2	
		TKBO1 (in the case of output from P20)	HS (high-speed main) mode	$4.0~V \leq V_{DD} \leq 5.5~V$			1.5	MHz
				$2.7 \text{ V} \le \text{V}_{\text{DD}} < 4.0 \text{ V}$			1.2	
				$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			1	
			LS (low-speed main) mode	$4.0~V \leq V_{DD} \leq 5.5~V$			1.5	
				$2.7~V \leq V_{DD} < 4.0~V$			1.2	
				$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			1	
				$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}$			0.75	
			LP (low-power main) mode	$1.8 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			0.5	
			LV (low-voltage main) mode	$4.0~V \leq V_{DD} \leq 5.5~V$			1.5	
				$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 4.0 \text{ V}$			1.2	
				$2.4 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$			1	
				$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}$			0.75	
				$1.6 \text{ V} \le \text{V}_{DD} < 1.8 \text{ V}$			0.5	
PCLBUZ0, PCLBUZ1 output frequency	fPCL	HS (high-speed main) mode		$4.0~V \le EV_{DD} \le 5.5~V$			16	MHz
				$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			8	
				$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			4	
				$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			2	
		LS (low-speed main) mode		$1.8~V \le EV \text{DD} \le 5.5~V$			4	
				$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			2	
		LP (low-power main) mode		$1.6~V \le EV_{DD} \le 5.5~V$			1	
		LV (low-voltage main) mode		$1.8~V \le EV_{DD} \le 5.5~V$			4	
				$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V}$			2	
Interrupt input high-/ low-level width	tinth,	INTP0 to INTP2, INTP9		$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	1			μs
	t INTL	INTP3 to INTP8, INTP10, INTP11		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$	1	1		1
Key interrupt input low-level width	tĸĸ	KR0 to KR7		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$	250			ns
				1.6 V ≤ EVDD < 1.8 V	1			μs
RESET low-level	trsl			1	10			μs

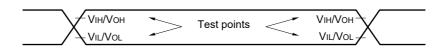
(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

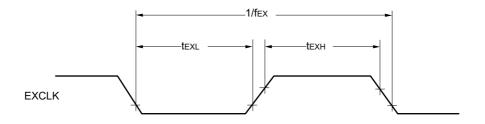
Note When duty is 50%.



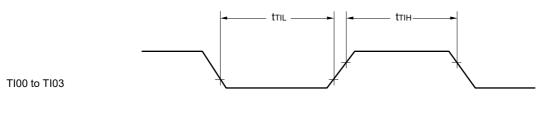
AC Timing Test Points

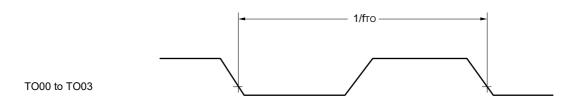


External System Clock Timing

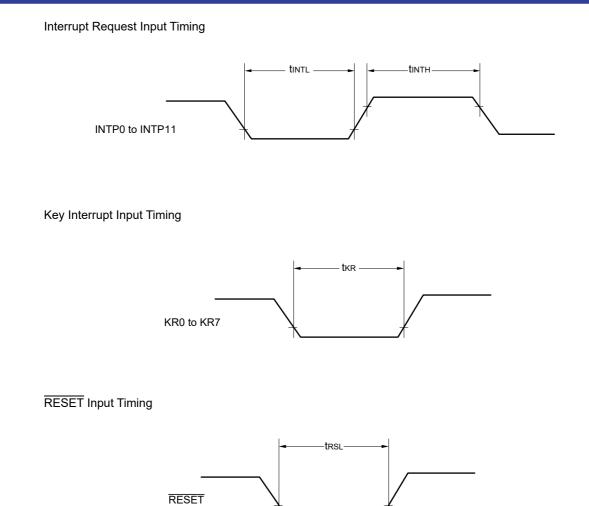


TI/TO Timing











2.5 Peripheral Functions Characteristics

AC Timing Test Points

Viн/Voн VIH/VOH Test points VIL/VOL . VIL/VOL



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

When P01, P30, P31 and P54 are used as TxDq pins (TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-sp Mo			oeed main) ode		ower main) ode	LV (low-vol Mo		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		$2.7~V \leq EV_{DD} \leq 5.5V$		fмск/6		fмск/6		fмск/6		fмск/6	bps
Note 1, 2		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 3$		4.0		1.3		0.1		0.6	Mbps
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		fмск/6		fмск/6		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 3$		4.0		1.3		0.1		0.6	Mbps
		$1.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		fмск/6		fмск/6		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 3$		4.0		1.3		0.1		0.6	Mbps
		$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	-	_		fмск/6		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} Note 3$	_	_		1.3		0.1		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. Following conditions must be satisfied on low level interface of EVDD < VDD.

 $2.4~\text{V} \leq \text{EV}_\text{DD}$ < 2.7 V: MAX.2.6 Mbps

 $1.8~V \leq EV_{DD}$ < 2.4 V: MAX.1.3 Mbps

 $1.6 \text{ V} \leq \text{EV}_{\text{DD}} < 1.8 \text{ V}$: MAX.0.6 Mbps

 $\label{eq:Note 3.} \qquad \mbox{The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:}$

HS (high-speed main) mode:	24 MHz (2.7 V \leq EVDD \leq 5.5 V)
	16 MHz (2.4 V \leq EVDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq EVDD \leq 5.5 V)
LP (low-power main) mode:	1 MHz (1.8 V \leq EVDD \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq EVDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



When P20 is used as TxD1 pin

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Parameter	Sym bol	Conditions		h-speed) Mode		peed main) ode	• •	ower main) ode	·	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Notes 1, 3		1.5		1.3		0.1		0.6	Mbps
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Notes 1, 3}$		1.2		1.2		0.1		0.6	Mbps
		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Notes 1, 3}$		1.0		1.0		0.1		0.6	Mbps
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$				fмск/6 Notes 1, 2		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Notes 1, 3}$				0.6		0.1		0.6	Mbps
		$1.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$								fмск/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}Notes 1, 3$		Using prohibited		Using		Using		0.5	Mbps
		$1.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$				prohibited		prohibited		fмск/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Notes 1, 3}$								0.5	Mbps

Note 1. fmcκ is a frequency selected by setting the CKS bit in the SPS and SMR registers.

Note 2. The transfer rate of 4800 bps is only supported in the SNOOZE mode.

Note that the SNOOZE mode is not supported when fHOCO is 48 MHz.

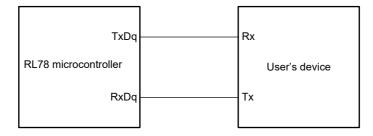
Note 3. fCLK in each operating mode is as follows.:

HS (high-speed main) mode:	24 MHz (2.7 V \leq VDD \leq 5.5 V)
	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq VDD \leq 5.5 V)
LP (low-power main) mode:	1 MHz (1.8 V \leq VDD \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq VDD \leq 5.5 V)

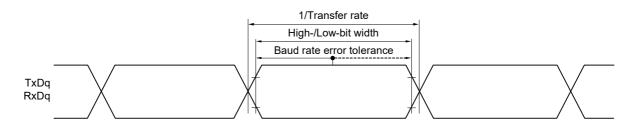
Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3 and 5)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions	HS (high-s Mo	peed main) ode		beed main) bde	· ·	ower main) ode	LV (low-vol Mo	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tkcy1≥2/fclk	83.3		250		2000		500		ns
SCKp high-/low-level width	tĸ∟1	$\begin{array}{l} 4.0 \text{ V} \leq \text{EVDD} \\ \leq 5.5 \text{ V} \end{array}$	tксү1/2 - 7		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		2.7 V ≤ EVDD ≤ 5.5 V	tксү1/2 - 10								ns
SIp setup time (to SCKp↑) _{Note 1}	tsıĸı	$\begin{array}{l} 4.0 \text{ V} \leq \text{EVDD} \\ \leq 5.5 \text{ V} \end{array}$	23		110		110		110		ns
		$\begin{array}{l} 2.7 \ \text{V} \leq \text{EVDD} \\ \leq 5.5 \ \text{V} \end{array}$	33								ns
SIp hold time (from SCKp↑) Note 2	tksi1		10		10		10		10		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 20 pF Note 4		10		20		20		20	ns

(TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))



(3) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	C	conditions	HS (high-s Mo	,	LS (low main)	/-speed Mode	LP (Lov main)	v-power mode	LV (low- main)	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tkCY1	tkcy1 ≥ 4/fclk	$2.7~V \leq EV_{\text{DD}} \leq 5.5~V$	167		500		4000		1000		ns
time			$2.4~V \leq EV_{\text{DD}} \leq 5.5~V$	250								
			$1.8~V \le EV_{\text{DD}} \le 5.5~V$	500								
			$1.7~V \leq EV_{DD} \leq 5.5~V$	1000		1000						
			$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$	Using prohibited		-						
SCKp high-/	tкнı,	$4.0 V \le EV_{DD}$	≤ 5.5 V	tксү1/2-12		tксү1/2		tксү1/2		tксү1/2		ns
low-level width	tĸ∟1	$2.7 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	tксү1/ 2- 18		- 50		- 50		- 50		
width		$2.4 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	tксү1/2 - 38								
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	tксү1/2 - 50								
		$1.7 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	tксү1/2 - 100		tксү1/2		tксү1/2		tксү1/2		
		1.6 V ≤ EVDD 5	≤ 5.5 V	Using prohibited		- 100		- 100		- 100		
SIp setup	tsik1	$4.0 V \le EV_{DD}$	≤ 5.5 V	44		110		110		110		ns
time (to SCKp↑)		$2.7 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V									
Note 1		$2.4 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	75								
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	110								
		$1.7 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	220		220		220		220		
		1.6 V ≤ EVDD :	≤ 5.5 V	Using prohibited								
SIp hold	tĸsı1	$1.7 \text{ V} \leq \text{EV}_{\text{DD}}$	≤ 5.5 V	19		19		19		19		ns
time (from SCKp↑) _{Note 2}		1.6 V ≤ EVDD :	≤ 5.5 V	Using prohibited								
Delay time	tkso1	C = 30 pF	$1.7~V \leq EV_{DD} \leq 5.5~V$		33.4		33.4		33.4		33.4	ns
from SCKp↓ to SOp output ^{Note 3}		Note 4	$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		Using prohibited							

When P01, P32, P53, P54 and P56 are used as SOmn pins

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. fMcK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

When P20 is used as SO10 pin

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	С	conditions		h-speed Mode		/-speed Mode		v-power mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	t КСҮ1	tĸcy1 ≥ 4/fclĸ	$4.0~V \leq V_{DD} \leq 5.5~V$	600		600		4000		1000		ns
time			$2.7~V \leq V_{DD} \leq 5.5~V$	850		850						
			$2.4~V \leq V_{DD} \leq 5.5~V$	1000		1000						
			$1.8~V \leq V_{\text{DD}} \leq 5.5~V$	—		1500				1500		
			$1.7~V \le V_{\text{DD}} \le 5.5~V$	—		—		—		2000		1
			$1.6~V \leq V_{DD} \leq 5.5~V$	_		—		_				1
SCKp high-/ low-level	tкн1, tк∟1	$4.0~V \leq V_{DD} \leq$	5.5 V	tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
width		$2.7~V \leq V_{DD} \leq$	5.5 V	tксү1/2 - 18								
		$2.4~V \leq V_{DD} \leq$	5.5 V	tксү1/2 - 38								
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq$	5.5 V	_								
		$1.7~V \leq V_{DD} \leq$	5.5 V	—		—		—		tксү1/2		
		$1.6~V \leq V_{DD} \leq$	5.5 V	—		—		—		- 100		
SIp setup	tsik1	$4.0~V \leq V_{DD} \leq$	5.5 V	44		110		110		110		ns
time (to SCKp↑)		$2.7~V \leq V_{DD} \leq$	5.5 V									
Note 1		$2.4~V \leq V_{DD} \leq$	5.5 V	75								
		$1.8~V \leq V_{DD} \leq$	5.5 V	—								
		$1.7~V \leq V_{DD} \leq$	5.5 V	—		—		—		220		1
		$1.6~V \leq V_{DD} \leq$	5.5 V	—		—		—				1
SIp hold	tksi1	$2.4~V \leq V_{DD} \leq$	5.5 V	19		19		19		19		ns
time (from SCKp↑)		$1.8~V \leq V_{DD} \leq$	5.5 V	—								
Note 2		$1.6~V \leq V_{DD} \leq$	5.5 V	—		—		—				
Delay time	tkso1	C = 30 pF	$2.4~V \le V_{DD} \le 5.5~V$		150		250		250		300	ns
from SCKp↓		Note 4	$1.8 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$		—	1						
to SOp output ^{Note 3}			$1.6~V \le V_{DD} \le 5.5~V$		—		—		—			

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 4 and 12)

Remark 2. fMck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

(1/2)

(4) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Condi	tions	HS (high-sı Mo	peed main) ode	LS (low-sp Mo	eed main) de		w-power mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү2	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V$	fмск > 20 MHz	8/fмск		—		_		—		ns
Note 3			fмск ≤ 20 MHz	6/fмск		6/fмск		6/fмск		6/fмск		
		$2.7~V \leq EV_{\text{DD}} \leq 5.5~V$	fмск > 16 MHz	8/fмск		—				—	—	
			fмск ≤ 16 MHz	6/fмск		6/fмск		6/fмск		6/fмск		
		$2.4~V \leq EV_{DD} \leq 5.5~V$		6/fмск and 500								
		$1.8~V \leq EV_{DD} \leq 5.5~V$		6/fмск and 750								
		$1.7~V \leq EV_{DD} \leq 5.5V$		6/fмск and 1500		6/fмск and 1500						
		$1.6~V \leq EV_{\text{DD}} \leq 5.5~V$		-								
SCKp high-/ low-level width	tкн2, tк∟2	$4.0~V \leq EV_{DD} \leq 5.5~V$		tксү2/2 - 7		tксү2/2 - 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~V \leq EV_{DD} \leq 5.5~V$		tксү2/2 - 8		tксү2/2 - 8		tксү2/2 - 8		tксү2/2 - 8		
		$1.8~V \leq EV_{DD} \leq 5.5~V$		tксү2/2 - 18		tксү2/2 - 18		tксү2/2 - 18		tксү2/2 - 18		
		$1.7~V \leq EV_{DD} \leq 5.5~V$		tксү2/2 - 66		tксү2/2 - 66		tксү2/2 - 66		tксү2/2 - 66		
		$1.6~V \leq EV_{\text{DD}} \leq 5.5~V$										
SIp setup time (to SCKp↑)	tsıк2	$2.7~V \leq EV_{DD} \leq 5.5~V$		1/fмск + 20		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
Note 1		$1.8~V \leq EV_{DD} \leq 5.5~V$		1/fмск + 30		1/fмск + 30		1/fмск + 30		1/fмск + 30		
		$1.7~V \leq EV_{DD} \leq 5.5~V$		1/fмск + 40		1/fмск + 40		1/fмск + 40		1/fмск + 40		
		$1.6~V \leq EV_{\text{DD}} \leq 5.5~V$		-								
Slp hold time (from SCKp↑)	tksi2	$1.8~V \leq EV_{DD} \leq 5.5~V$		1/fмск + 31		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Note 2		$1.7~V \leq EV_{DD} \leq 5.5~V$		1/fмск + 250		1/fмск + 250		1/fмск + 250		1/fмск + 250		
	1	$1.6~V \leq EV_{\text{DD}} \leq 5.5~V$		_]						

When P01, P32, P53, P54 and P56 are used as SOmn pins (TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(2/2)

Parameter	Symbol		Conditions		peed main) ode	• •	beed main) bde	· ·	ower main) ode	LV (low-vol Mo	tage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Delay time from SCKp↓ to SOp output	tĸso2	C = 30 pF Note 2	$2.7~V \leq EV_{DD} \leq 5.5~V$		2/fмск + 44		2/fмск + 110		2/fмск + 110		2/fмск + 110	ns
Note 1			$2.4~V \leq EV_{DD} \leq 5.5~V$		2/fмск + 75							
			$1.8~V \leq EV_{DD} \leq 5.5~V$		2/fмск + 110							
			$1.7~V \leq EV_{DD} \leq 5.5~V$		2/fмск + 220		2/fмск + 220		2/fмск + 220		2/fмск + 220	
			$1.6~V \leq EV_{DD} \leq 5.5~V$		-							
SSI00 setup time	tssiĸ	DAPmn = 0	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	120		120		120		120		ns
			$1.8~V \leq V_{\text{DD}} < 2.7~V$	200		200		200		200		
			$1.7~V \leq V_{\text{DD}} < 1.8~V$	400		400		400		400		
			$1.6~V \leq V_{\text{DD}} < 1.7~V$	_					-			
		DAPmn = 1	$2.7~V \leq V_{DD} \leq 5.5~V$	1/fмск + 120		1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	1/fмск + 200		1/fмск + 200		1/fмск + 200		1/fмск + 200		
			$1.7 \text{ V} \leq \text{V}_{\text{DD}} < 1.8 \text{ V}$	1/fмск + 400		1/fмск + 400		1/fмск + 400		1/fмск + 400		
			$1.6~V \leq V_{\text{DD}} < 1.7~V$	_				-				
SSI00 hold time	tĸssi	DAPmn = 0	$2.7~V \leq V_{DD} \leq 5.5~V$	1/fмск + 120		1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	1/fмск + 200		1/fмск + 200		1/fмск + 200		1/fмск + 200		
			$1.7 \text{ V} \le \text{V}_{\text{DD}} < 1.8 \text{ V}$	1/fмск + 400		1/fмск + 400		1/fмск + 400		1/fмск + 400		
			$1.6 \text{ V} \leq V_{\text{DD}} < 1.7 \text{ V}$	-				1		1		1
		DAPmn = 1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	120		120		120		120		ns
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	200		200		200		200		1
			$1.7 \text{ V} \leq \text{V}_{\text{DD}} < 1.8 \text{ V}$	400		400		400		400		
			$1.6~V \leq V_{\text{DD}} < 1.7~V$	_]]]		

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. C is the load capacitance of the SOp output lines.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



Parameter	Symbol	Cond	litions		peed main) ode		beed main) bde	-	v-power mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t ксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	fмск > 20 MHz	14/fмск		—		_		_		ns
Note 5			fмск ≤ 20 MHz	12/fмск		12/fмск		12/fмск		12/fмск		
		$2.7~V \leq V_{DD} \leq 5.5~V$	f _{мск} > 16 MHz	14/fмск and 850		_		_		_		
			fмск ≤ 16 MHz	12/fмск and 850		12/fмск		12/fмск		12/fмск		
		$2.4~V \leq V_{DD} \leq 5.5~V$		12/fмск and 1000		12/fмск		12/fмск		12/fмск		
		$1.8~V \leq V_{\text{DD}} \leq 5.5~V$		_		12/fмск		12/fмск		12/fмск		
		$1.7~V \leq V_{\text{DD}} \leq 5.5V$		_		-		-		12/fмск		
		$1.6~V \leq V_{\text{DD}} \leq 5.5~V$		—		—						
SCKp high-/ low-level width	tкн2, tкL2	$4.0~V \leq V_{DD} \leq 5.5~V$		tксү2/2 - 7		tксү2/2 - 7		tксү2/2 - 7		tксү2/2 - 7		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү2/2 - 8		tксү2/2 - 8		tксү2/2 - 8		tксү2/2 - 8		
		$1.8~V \leq V_{DD} \leq 5.5~V$		-		tксү2/2 - 18		tксү2/2 - 18		tксү2/2 - 18		
		$1.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		_		_		_		tксү2/2 -		1
		$1.6~V \le V_{\text{DD}} \le 5.5~V$		_		—		_		66		
SIp setup time (to SCKp↑)	tsik2	$2.7~V \leq V_{DD} \leq 5.5~V$		1/fмск + 20		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
Note 1		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		1/fмск + 30							-	
		$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		_		-				-		-
		$1.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$		_		_		_		1/fмск		-
		$1.6~V \le V_{\text{DD}} \le 5.5~V$		- T		-		_		+ 40		
SIp hold time (from SCKp↑)	tĸsı2	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск + 31		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Note 2		$1.8~V \leq V_{\text{DD}} \leq 5.5~V$		-		1/fмск + 31		1/fмск + 31		1/fмск + 31		
		$1.7~V \leq V_{\text{DD}} \leq 5.5~V$		_		_		_		1/fмск		
		$1.6~V \leq V_{\text{DD}} \leq 5.5~V$		_		-		_		+ 250		
Delay time from SCKp↓ to SOp	tĸso2	C = 30 pF Note 4	$2.7~V \leq V_{DD} \leq 5.5~V$		2/fмск + 160		2/fмск + 260		2/fмск + 260		2/fмск + 260	ns
output ^{Note 3}			$2.4~V \leq V_{DD} \leq 5.5~V$		2/fмск + 190							
			$1.8~V \leq V_{\text{DD}} \leq 5.5~V$		—	1						
			$1.7~V \leq V_{DD} \leq 5.5~V$		-		-		—		2/fмск	1
			$1.6~V \leq V_{DD} \leq 5.5~V$		—		_]	+ 320	

When P20 is used as SO10 pin

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

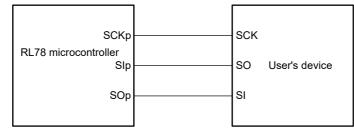
Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM

numbers (g = 0, 4 and 12)

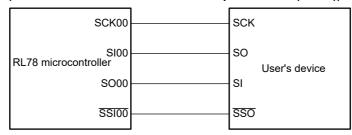
Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode connection diagram (during communication at same potential)

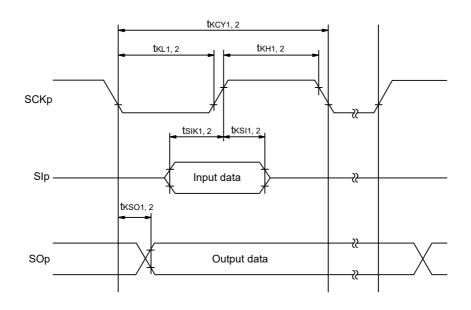


Simplified SPI (CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))

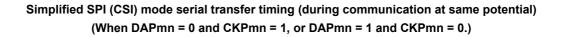


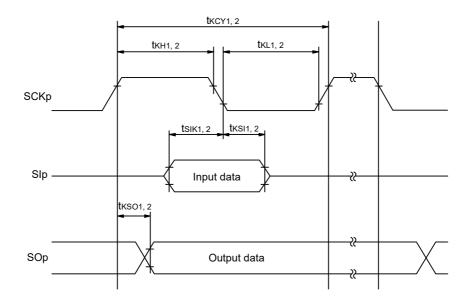
Remark p: CSI number (p = 00, 01, 10 and 11)





Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark 1. p: CSI number (p = 00, 01, 10 and 11) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03)

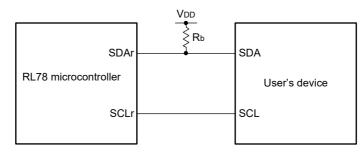
(5) During communication at same potential (simplified I²C mode)

Parameter	Symbol	Conditions		speed main) ode		beed main) bde		v-power mode		-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$		1000 Note 1		400 Note 1		250 Note 1		400 Note 1	kHz
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} &= 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$		400 Note 1							
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq \mbox{EV}_{\mbox{DD}} < 2.7 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5 \mbox{ k}\Omega \end{array}$		300 Note 1		300 Note 1		250 Note 1		300 Note 1	
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{DD} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$		250 Note 1		250 Note 1		250 Note 1		250 Note 1	
		$\label{eq:linear} \begin{split} 1.6 \mbox{ V} &\leq E \mbox{ V}_{DD} < 1.8 \mbox{ V}, \\ C_b &= 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k} \Omega \end{split}$		-							
Hold time when SCLr = "L"	tLOW	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD}} \leq 5.5 \ \text{V}, \\ \\ C_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	475		1150		1150		1150		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq E V_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} &= 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$	1150								
		$\label{eq:linear} \begin{split} 1.8 \mbox{ V} &\leq \mbox{EV}_{\mbox{DD}} < 2.7 \mbox{ V}, \\ C_{\mbox{b}} &= 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5 \mbox{k} \Omega \end{split}$	1550		1550		1550		1550		
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{DD} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	1850		1850		1850		1850		
		$\label{eq:bound} \begin{array}{l} 1.6 \mbox{ V} \leq E \mbox{ V}_{\mbox{\scriptsize DD}} < 1.8 \mbox{ V}, \\ C_{\mbox{\scriptsize b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\scriptsize b}} = 5 \mbox{Ω} \end{array}$	-		-				-		
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD}} \leq 5.5 \ \text{V}, \\ \\ C_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	475		1150		1150		1150		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq E V_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_{\text{b}} &= 100 \ \text{pF}, \ R_{\text{b}} = 3 \ \text{k}\Omega \end{split}$	1150		-						
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq E \mbox{ V}_{\mbox{\scriptsize DD}} < 2.7 \mbox{ V}, \\ C_{\mbox{\scriptsize b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\scriptsize b}} = 5 \mbox{Ω} \end{array}$	1550		1550		1550		1550		
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{DD} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	1850		1850		1850		1850		
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq E \mbox{ V}_{\mbox{\scriptsize DD}} < 1.8 \mbox{ V}, \\ C_{\mbox{\scriptsize b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\scriptsize b}} = 5 \mbox{Ω} \end{array}$	-		-				-		
Data setup time (reception)	tsu: dat	$\begin{array}{l} 2.7 \ V \leq E V_{DD} \leq 5.5 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 85 Note 2		1/fмск + 145 Note 2		1/fмск + 145 Note 2		1/fмск + 145 Note 2		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD}} \leq 5.5 \ \text{V}, \\ C_b &= 100 \ \text{pF}, \ R_b = 3 \ \text{k}\Omega \end{split}$	1/fмск + 145 Note 2								
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD} < 2.7 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	1/fмск + 230 Note 2		1/fмск + 230 Note 2		1/fмск + 230 Note 2		1/fмск + 230 Note 2		
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\rm DD} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fмск + 290 Note 2		
		$\label{eq:linear} \begin{array}{l} 1.6 \text{ V} \leq \text{EV}_{\text{DD}} < 1.8 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 5 \text{ k}\Omega \end{array}$	-		-				-		
Data hold time (transmission)	thd: dat	$\begin{array}{l} 2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{array}$	0	305	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD} \leq 5.5 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 3 \mbox{ k}\Omega \end{array}$		355	1	355		355	1	355	
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq E \mbox{ V}_{\rm DD} < 2.7 \mbox{ V}, \\ \mbox{ C}_{\rm b} = 100 \mbox{ pF}, \mbox{ R}_{\rm b} = 5 \mbox{ k} \Omega \end{array}$	1	405	1	405		405	1	405	
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{DD} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	1								
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	-	-	1						

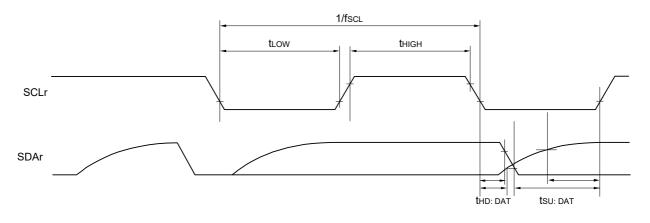
(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)



- **Note 1.** The value must be equal to or less than fMCK/4.
- **Note 2.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the normal input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).
 - Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- Remark 1. Rb[Ω]: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance r: IIC number (r = 00, 01, 10 and 11), g: PIM number (g = 0, 3 and 5), h: POM number (h = 0, 3 and 5)
- Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3), mn = 00 to 03)



(1/2)

RL78/G11

(6) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (UART mode) (dedicated baud rate generator output)

(TA = -40 to +85	$5^{\circ}C$, 1.8 V \leq EVDD \leq VDD \leq	\leq 5.5 V. Vss = 0 V)
(17. 10.00.00	• •, • = = • • • • = • • • •	,

Parameter	Symbol		Conditions		gh-speed) Mode		w-speed) Mode		w-power) mode		ow-voltage in) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$		fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
			$2.7 V \le EV_{DD} < 4.0 V,$ $2.3 V \le V_b \le 2.7 V$		fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
			Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} Note 3		4.0		1.3		0.1		0.6	Mbps
			$\begin{array}{l} 1.8 \ V \leq EV_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		fмск/6 Notes 1, 2, 4		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.1		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with $EV_{DD} \ge Vb$.

 $\label{eq:Note 3.} \qquad \mbox{The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:}$

HS (high-speed main) mode:	24 MHz (2.7 V \leq VDD \leq 5.5 V)
	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq VDD \leq 5.5 V)
LP (low-power main) mode:	1 MHz (1.8 V \leq VDD \leq 5.5 V)
LV (low-voltage main) mode:	4 MHz (1.6 V \leq VDD \leq 5.5 V)

Note 4.The following conditions are required for low voltage interface when EVDD < VDD $2.4 V \le EVDD < 2.7 V$: MAX. 2.6 Mbps $1.8 V \le EVDD < 2.4 V$: MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb[V]: Communication line voltage

Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)

Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(2/2)

		,		•••								(2,2)
Parameter	Symbol		Conditions		igh-speed ı) Mode	LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$		Note 1		Note 1		Note 1		Note 1	bps
			$\label{eq:constraint} \begin{array}{l} Theoretical value of the \\ maximum transfer rate \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 1.4 \mbox{ k}\Omega, \\ V_b = 2.7 \mbox{ V} \end{array}$		2.8 Note 2		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3		Note 3		Note 3		Note 3	bps
			$\label{eq:constraint} \hline Theoretical value of the maximum transfer rate \\ C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega, \\ V_b = 2.3 \text{ V} \\ \hline \hline \end{matrix}$		1.2 Note 4		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			$\begin{array}{l} 1.8 \ V \leq EV_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		Notes 5, 6		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			$\label{eq:constraint} \begin{array}{l} Theoretical value of the \\ maximum transfer rate \\ C_b = 50 \ pF, \ R_b = 5.5 \ k\Omega, \\ V_b = 1.6 \ V \end{array}$		0.43 Note 7		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}\text{DD} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$

1

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $2.7 \text{ V} \le \text{EVDD} \le 4.0 \text{ V}$ and $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$

1

Baud rate error (theoretical value) =

$$\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}$$

$$(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 4.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EV_{DD} \ge V_b$.

Note 6. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $1.8 \text{ V} \le \text{EV}\text{DD} < 3.3 \text{ V}$ and $1.6 \text{ V} \le \text{V}\text{b} \le 2.0 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{|Transfer rate \times 2|} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{|Transfer rate}) \times 100 [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

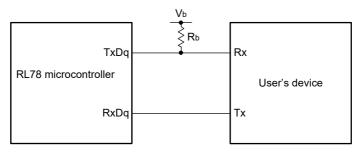
Note 7. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

4

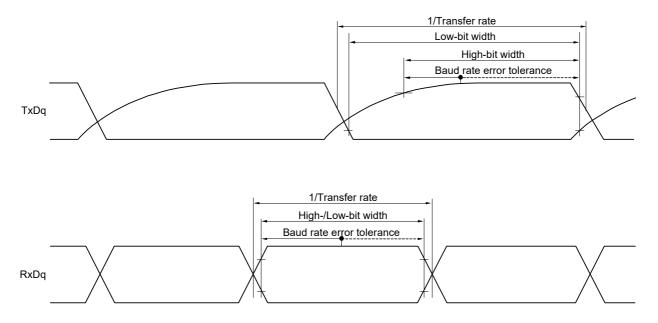
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. Rb[Ω]: Communication line (TxDq) pull-up resistance, Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)

Remark 3. fMck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Sym bol		Conditions	HS (hig main)	h-speed Mode	`	/-speed Mode	`	v-power mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t КСҮ1	tксү1 ≥ 2/f с∟к		200		1150		1150		1150		ns
		tксү1 ≥ 2/f с∟к	$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	300								ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq \\ 2.7 \ V \leq V_b \leq 4. \\ C_b = 20 \ pF, \ R_b \end{array}$	0 V,	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V},$ $2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ $C_b = 20 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega$ $4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}.$		tксү1/2 - 120		tксү1/2 - 120		tксү1/2 - 120		tксү1/2 - 120		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 2.7 \ V \leq V_b \leq 4. \\ C_b = 20 \ pF, \ R_b \end{array}$	$C_{b} = 20 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$ $4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$ $C_{b} = 20 \text{ pF}, R_{b} = 1.4 \text{ k}\Omega$ $2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$			tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 V \le EVDD <$ 2.3 V $\le V_b \le 2$. C _b = 20 pF, R _b	7 V,	tксү1/2 - 10								
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq \\ 2.7 \ V \leq V_b \leq 4. \\ C_b = 20 \ pF, \ R_b \end{array}$	0 V,	58		479		479		479		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < \\ 2.3 \ V \leq V_b \leq 2. \\ C_b = 20 \ pF, \ R_b \end{array}$	7 V,	121								
SIp hold time (from SCKp↑) ^{Note 1}	tksi1	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq \\ 2.7 \ V \leq V_b \leq 4. \\ C_b = 20 \ pF, \ R_b \end{array}$	0 V,	10		10		10		10		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < \\ 2.3 \ V \leq V_b \leq 2. \\ C_b = 20 \ pF, \ R_b \end{array}$	7 V,									
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq \\ 2.7 \ V \leq V_b \leq 4. \\ C_b = 20 \ pF, \ R_b \end{array}$	0 V,		60		60		60		60	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < \\ 2.3 \ V \leq V_b \leq 2. \\ C_b = 20 \ pF, \ R_b \end{array}$	7 V,		130		130		130		130	
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸı	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq \\ 2.7 \ V \leq V_b \leq 4. \\ C_b = 20 \ pF, \ R_b \end{array}$	0 V,	23		110		110		110		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < \\ 2.3 \ V \leq V_b \leq 2. \\ C_b = 20 \ pF, \ R_b \end{array}$	7 V,	33								
SIp hold time (from SCKp↓) Note 2	tksi1	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq \\ 2.7 \; V \leq V_b \leq 4. \\ C_b = 20 \; pF, \; R_b \\ \hline 2.7 \; V \leq EV_{DD} \leq \end{array}$	0 V, = 1.4 kΩ	10		10		10		10		ns
		$\begin{array}{l} 2.3 \ V \leq V_b \leq 2. \\ C_b = 20 \ pF, \ R_b \end{array}$										

(TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)



(2/2)

(TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Sym bol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		· ·		Low-power LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 20 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		10		10		10		10	ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$									

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For ViH and ViL, see the DC characteristics with TTL input buffer selected.

Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 5)

Remark 3. fмcκ: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))



(1/2)

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Sym bol		Conditions		h-speed Mode		v-speed Mode	LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
	IOU			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tkcy1 ≥ 4/fclk	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	300		1150		1150		1150		ns
			$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		-						ns
			$\label{eq:VDD} \begin{split} & 1.8 \; V \leq EV_{DD} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V \; ^{Note}, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	1150		-						ns
SCKp high- level width	tкн1	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq$ Cb = 30 pF, Rb	≤ 5.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	tксү1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} <$ Cb = 30 pF, Rb	< 4.0 V, 2.3 V \le V _b \le 2.7 V, = 2.7 kΩ	tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		ns
		1.8 V ≤ EV _{DD} < _{Note,} C _b = 30 pF, R _b	s 3.3 V, 1.6 V s V _b s 2.0 V = 5.5 kΩ	tксү1/2 - 458		tксү1/2 - 458		tксү1/2 - 458		tксү1/2 - 458		ns
SCKp low-level width	tĸ∟1	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq$ Cb = 30 pF, Rb	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$ = 1.4 k Ω	tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF, R}_{\text{b}}$	< 4.0 V, 2.3 V \le V _b \le 2.7 V, = 2.7 kΩ	tксү1/2 - 18								
		$\begin{array}{l} 1.8 \ V \leq EV_{DD} < \\ & \\ Note_{,} \\ C_{b} = 30 \ pF, \ R_{b} \end{array}$	= 3.3 V, 1.6 V \leq V _b \leq 2.0 V = 5.5 kΩ	tксү1/2 - 50								ns

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note Use it with $EV_{DD} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)



(2/2)

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

HS (high-speed LS (low-speed LP (Low-power LV (low-voltage Sym Conditions main) Mode main) Mode main) mode main) Mode Parameter Unit bol MIN MIN MIN MIN MAX. MAX. MAX. MAX. 479 479 $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ 81 479 SIp setup tsik1 ns time $C_b = 30 \text{ pF}$. $R_b = 1.4 \text{ k}\Omega$ (to SCKp↑) $2.7~V \leq EV_{DD}$ < 4.0 V, 2.3 V $\leq V_b \leq 2.7$ V, 177 Note 1 $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 479 $1.8 \text{ V} \le \text{EV}_{\text{DD}}$ < 3.3 V, 1.6 V $\le \text{V}_{b} \le 2.0 \text{ V}^{\text{Note 3}}$, $C_b = 30 \text{ pF}$. $R_b = 5.5 \text{ k}\Omega$ 19 Slp hold time $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ 19 19 19 tksi1 ns (from SCKp↑) $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$ Note 1 $2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}.$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 1.8 V < EVDD < 3.3 V. 1.6 V < Vb < 2.0 V Note 3. C_b = 30 pF, R_b = 5.5 k Ω Delay time tks01 $4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ 100 100 100 100 ns from SCKp↓ C_b = 30 pF, R_b = 1.4 k Ω to SOp $2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ 195 195 195 195 ns output Note 1 $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 483 483 483 483 $1.8 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}^{\text{Note 3}},$ ns $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ 44 110 110 110 SIp setup tsik1 $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ ns time C_b = 30 pF, R_b = 1.4 k Ω (to SCKp↓) $2.7~V \leq EV_{DD}$ < 4.0 V, 2.3 V $\leq V_b \leq 2.7$ V, Note 2 C_b = 30 pF, R_b = 2.7 k Ω $1.8 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$ Note 3, 110 $C_b = 30 \text{ pF}$. $R_b = 5.5 \text{ k}\Omega$ SIp hold time $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ 19 19 19 19 ns tksi1 (from SCKp1) C_b = 30 pF, R_b = 1.4 k Ω Note 2 $2.7~V \leq EV_{DD}$ < 4.0 V, 2.3 V $\leq V_b \leq 2.7$ V, $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 1.8 V \leq EV_{DD} < 3.3 V, 1.6 V \leq V_b \leq 2.0 V ^{Note 3}, $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ Delay time 25 25 25 25 $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ tkso1 ns from SCKp↑ C_b = 30 pF, R_b = 1.4 k Ω to SOp $2.7 \text{ V} \leq EV_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \leq V_b \leq 2.7 \text{ V},$ output Note 2 $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ 1.8 V \leq EV_{DD} < 3.3 V, 1.6 V \leq V_b \leq 2.0 V Note 3, $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

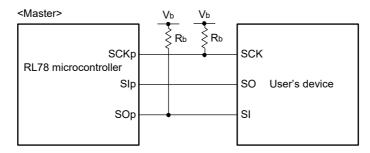
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with $EV_{DD} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For ViH and ViL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential)



Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

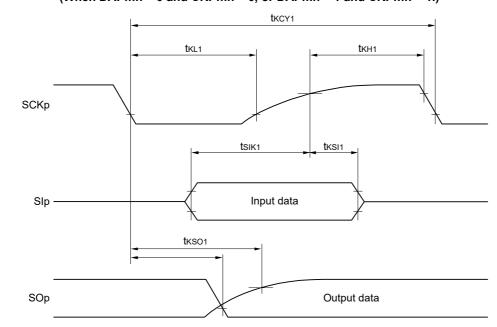
Remark 2. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 3. fmck: Serial array unit operation clock frequency

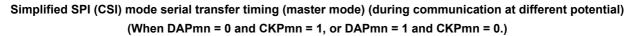
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

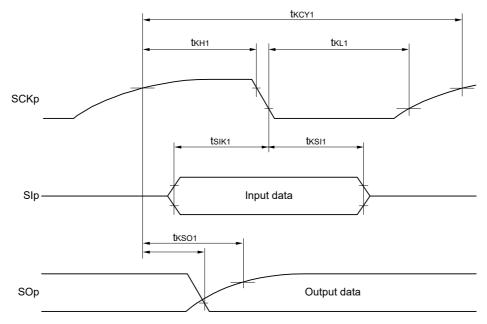
n: Channel number (mn = 00 to 03))





Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(9) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

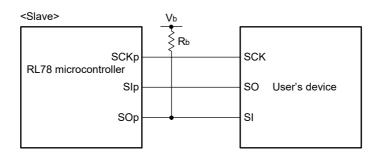
Parameter	Symb	с	onditions		h-speed Mode		v-speed Mode		v-power mode		-voltage Mode	Unit
	ol			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	t ксү2	$4.0~V \leq EV_{\text{DD}} \leq 5.5~V,$	20 MHz < f_{MCK} \leq 24 MHz	12/fмск		_		_		_		ns
time Note 1		$2.7~V \leq Vb \leq 4.0~V$	8 MHz < fмск ≤ 20 MHz	10/fмск		_		_		_		ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/fмск		_		_		ns
			fMCK ≤ 4 MHz	6/fмск		10/fмск		10/fмск		10/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 4.0 \text{ V},$	20 MHz < fмск ≤ 24 MHz	16/fмск		_		_		_		ns
		$2.3~V \leq Vb \leq 2.7~V$	16 MHz < fмск ≤ 20 MHz	14/fмск		_		_		_		ns
			8 MHz < fмск ≤ 16 MHz	12/fмск		_		_		_		ns
			4 MHz < fмск ≤ 8 MHz	8/fмск		16/fмск		_		_		ns
			fMCK ≤ 4 MHz	6/fмск		10/fмск		10/fмск		10/fмск		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} < 2.7 \text{ V},$	20 MHz < fмск ≤ 24 MHz	36/fмск		_		_		_		ns
		$1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$ Note 2	16 MHz < fмск ≤ 20 MHz	32/fмск		_		_		_		ns
		Note 2	8 MHz < fмск ≤ 16 MHz	26/fмск		_		_		_		ns
			4 MHz < fмск ≤ 8 MHz	16/fмск		16/fмск		_		_		ns
			fмск ≤ 4 MHz	10/fмск		10/fмск		10/fмск		10/fмск		ns
SCKp high-/	tкн2,	$4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}, 2.7$	$V \le Vb \le 4.0 V$	tксү2/2		tксү2/2		tkcy2/2		tксү2/2 -		ns
low-level width	tĸ∟2		- 12		- 50		- 50		50			
width		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3$	$V \le Vb \le 2.7 V$	tксү2/2 - 18		tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
										50 tксү2/2 -		
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6$	$5 \text{ V} \leq \text{Vb} \leq 2.0 \text{ V}$ Note 2	tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		1KCY2/2 - 50		ns
SIp setup	tsik2	4.0 V ≤ EV _{DD} ≤ 5.5 V, 2.7	$V \le Vb \le 4.0 V$	1/fмск		1/fмск		1/fмск		1/fмск +		ns
time (to				+ 20		+ 30		+ 30		30		
SCKp↑) Note 3		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V}$	$3 \text{ V} \leq \text{Vb} \leq 2.7 \text{ V}$	1/fмск		1/fмск		1/fмск		1/fмск +		ns
				+ 20		+ 30		+ 30		30		
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6$	$\delta V \le V_b \le 2.0 V$ Note 2	1/fмск + 30		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold	tksi2			1/fмск		1/fмск		1/fмск		1/fмск +		ns
time (from SCKp↑) _{Note 3}				+ 31		+ 31		+ 31		31		
Delay time from SCKp↓	tĸso2	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \\ C_b = 30 \ p\text{F}, \ R_b = 1.4 \ k\Omega \end{array}$	$V \leq V_b \leq 4.0 V$,		2/fмск + 120		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns
to SOp output ^{Note 4}		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, 2.3 \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	$3 \text{ V} \leq \text{Vb} \leq 2.7 \text{ V},$		2/fмск + 214		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns
		$\label{eq:VDD} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\rm DD} < 3.3 \mbox{ V}, \ 1.6 \\ C_b = 30 \mbox{ pF}, \ R_b = 5.5 \mbox{ k}\Omega \end{array}$	δ V \leq Vb \leq 2.0 V Note 2,		2/fмск + 573		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

(TA = -40 to 85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(Notes, Caution and Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EV_{DD} \ge V_b$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

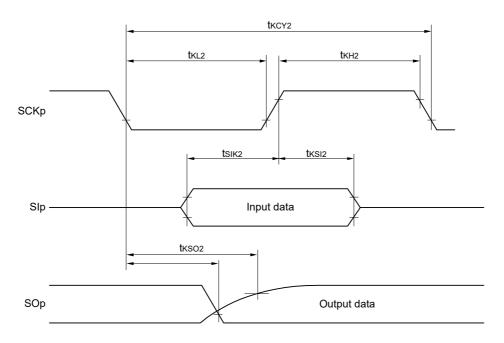
Simplified SPI (CSI) mode connection diagram (during communication at different potential)



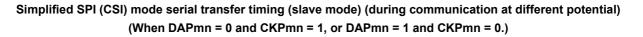
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00 to 03), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency

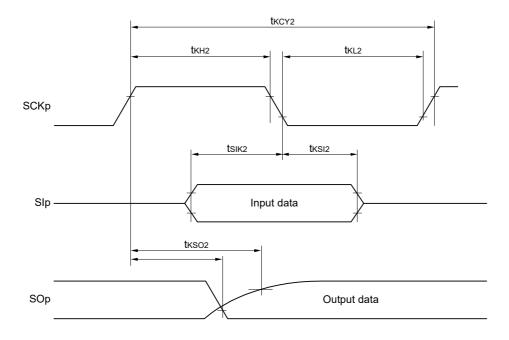
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))





Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(10) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (simplified I²C mode)

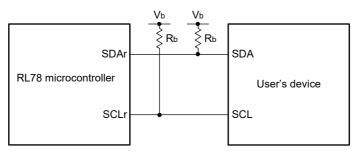
Parameter	Sym	Conditions		h-speed Mode		v-speed Mode	LP (Low-powe main) mode				Unit
	bol		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		1000 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		1000 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$		400 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ C_b &= 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		300 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
Hold time when SCLr	t∟ow	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	475		1550		1550		1550		ns
= "L"		$\label{eq:V_b} \begin{split} 2.7 \ V &\leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 50 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	475		1550		1550		1550		ns
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	1150		1550		1550		1550		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1150		1550		1550		1550		ns
		$\label{eq:Vote_state} \begin{array}{l} 1.8 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \mbox{Note 2}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	1550		1550		1550		1550		ns
Hold time when SCLr	tніgн	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	245		610		610		610		ns
= "H"		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	200		610		610		610		ns
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	675		610		610		610		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	600		610		610		610		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \mbox{Note 2}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	610		610		610		610		ns
Data setup time (reception)	tsu: DAT	$\label{eq:linear} \begin{split} 4.0 \ V &\leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ p\text{F}, \ R_b = 2.7 \ k\Omega \end{split}$	1/fмск + 135 Note 3		1/fмск + 190 Note 2		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$\label{eq:constraint} \begin{array}{l} 2.7 \ V \leq EV_{\rm DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 135 Note 3		1/fмск + 190 Note 2		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$\label{eq:linear} \begin{split} 4.0 \ V &\leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.8 \ k_\Omega \end{split}$	1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$\label{eq:constraint} \begin{array}{l} 2.7 \ V \leq EV_{\rm DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k_\Omega \end{array}$	1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \ V \leq EV_{DD} < 4.0 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \mbox{Note 2}, \\ C_b = 100 \ \mbox{pF}, \ R_b = 5.5 \ \mbox{k}\Omega \end{array}$	1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
Data hold time (transmission)	thd: Dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	305	0	305	0	305	0	305	ns
		$\label{eq:V_def} \begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	0	305	ns
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	0	355	0	355	0	355	0	355	ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	355	0	355	0	355	0	355	ns
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq EV_{DD} < 3.3 \ V, \ 1.6 \ V &\leq V_b \leq 2.0 \ V \ \text{Note 2}, \\ C_b &= 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	0	405	0	405	0	405	0	405	ns

(TA = -40 to 85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

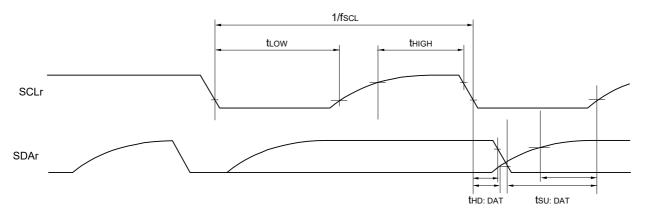


- **Note 1.** The value must be equal to or less than fMCK/4.
- Note 2. Use it with $EV_{DD} \ge V_b$.
- Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the N-ch open drain output (EVDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01, 10 and 11), g: PIM, POM number (g = 0, 3 and 5)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3), mn = 00 to 03)



2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	C	onditions		h-speed) mode		v-speed mode	•	v-power mode		-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	1
SCLA0 clock	fscl	Standard mode:	$2.7~V \leq EV_{DD} \leq 5.5~V$	0	100	0	100	0	100	0	100	kHz
frequency		fc∟ĸ ≥ 1 MHz	$1.8~V \le EV_{DD} \le 5.5~V$	0	100	0	100	0	100	0	100	kHz
			$1.7~V \leq EV_{DD} \leq 5.5~V$	0	100	0	100	0	100	0	100	kHz
			$1.6~V \leq EV_{DD} \leq 5.5~V$	-	_	0	100	0	100	0	100	kHz
Setup time of	tsu: sta	$2.7~V \le EV_{DD} \le 5$	5 V	4.7		4.7		4.7		4.7		μs
restart condition		$1.8 \text{ V} \leq EV_{DD} \leq 5$.5 V	4.7		4.7		4.7		4.7		μs
		$1.7 \text{ V} \leq EV_{DD} \leq 5$.5 V	4.7		4.7		4.7		4.7		μs
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	-	_	4.7		4.7		4.7		μs
Hold time Note 1	thd: STA	$2.7~V \leq EV_{DD} \leq 5$.5 V	4.0		4.0		4.0		4.0		μs
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
		$1.7 \text{ V} \le EV_{DD} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.6 \text{ V}$	5 V	-	_	4.0		4.0		4.0		μs
Hold time when	tLOW	$2.7~V \leq EV_{DD} \leq 5$.5 V	4.7		4.7		4.7		4.7		μs
SCLA0 = "L"		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.7		4.7		4.7		4.7		μs
		$1.7 \text{ V} \le EV_{DD} \le 5$.5 V	4.7		4.7		4.7		4.7		μs
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	-	_	4.7		4.7		4.7		μs
Hold time when	tніgн	$2.7 \text{ V} \le EV_{DD} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
SCLA0 = "H"		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
		$1.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	-	_	4.0		4.0		4.0		μs
Data setup time	tsu: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	250		250		250		250		ns
(reception)		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	250		250		250		250		ns
		$1.7 \text{ V} \leq EV_{DD} \leq 5$.5 V	250		250		250		250		ns
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	-	_	250		250		250		ns
Data hold time	thd: dat	$2.7 \text{ V} \le EV_{DD} \le 5$.5 V	0	3.45	0	3.45	0	3.45	0	3.45	μs
(transmission) Note 2		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	0	3.45	0	3.45	0	3.45	0	3.45	μs
Note 2		$1.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	0	3.45	0	3.45	0	3.45	0	3.45	μs
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	-	_	0	3.45	0	3.45	0	3.45	μs
Setup time of	tsu: sto	$2.7~V \le EV_{DD} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
stop condition		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.0		4.0		4.0		4.0		μs
		$1.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.0		4.0	1	4.0		4.0		μs
		$1.6 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	-		4.0	1	4.0		4.0	1	μs
Bus-free time	t BUF	$2.7 \text{ V} \leq EV_{DD} \leq 5$.5 V	4.7		4.7	1	4.7		4.7		μs
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5$.5 V	4.7		4.7	1	4.7		4.7		μs
		$1.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$.5 V	4.7	1	4.7	1	4.7		4.7	1	μs
		$1.6 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5 V	-	_	4.7		4.7		4.7		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of the DE DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω



(2) I²C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		speed	HS (high- speed main) mode		LS (low- speed main) mode		Low- ⁻ main) ode	LV (low- voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7~V \leq EV_{DD} \leq 5.5~V$	0	400	0	400	0	400	0	400	kHz
		fclk ≥ 3.5 MHz	$1.8~V \leq EV_{DD} \leq 5.5~V$	0	400	0	400	0	400	0	400	kHz
Setup time of restart	tsu: sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		0.6		0.6		0.6		0.6		μs
condition		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		0.6		0.6		0.6		0.6		μs
Hold time Note 1	thd: STA	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		0.6		0.6		0.6		0.6		μs
		$1.8 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$		0.6		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	t∟ow	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	1.3		1.3		1.3		1.3		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	1.3		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	tніgн	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	0.6		0.6		0.6		0.6		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	0.6		0.6		0.6		0.6		μs
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	100		100		100		100		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	100		100		100		100		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	0	0.9	0	0.9	0	0.9	0	0.9	μs
Note 2		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	0	0.9	0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tsu: sto	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	0.6		0.6		0.6		0.6		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		0.6		0.6		0.6		0.6		μs
Bus-free time	t BUF	$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$		1.3		1.3		1.3		1.3		μs
		$1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		1.3		1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of the DLAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 k Ω



(3) I²C fast mode plus

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

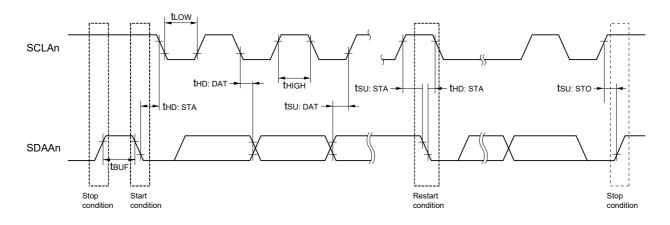
Parameter	Symbol	Conditions		speed	high- l main) ode	LS (low- speed main) mode		LP (Low- power main) mode		LV (low- voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fc∟k ≥ 10 MHz	·			-		kHz				
Setup time of restart condition	tsu: sta	$2.7 V \le EV_{DD} \le 5.5 V$ 0.26 — — —		_	-		μs					
Hold time ^{Note 1}	thd: STA	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		0.26		—		—		_		μs
Hold time when SCLA0 = "L"	t∟ow	$2.7~V \leq EV_{DD} \leq 5.5~V$		0.5		—		—		-	_	μs
Hold time when SCLA0 = "H"	tніgн	$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.$	5 V	0.26		—		—		-	_	μs
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.$	5 V	50		—		_		-	_	ns
Data hold time (transmission) Note 2	thd: dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		0	0.45	-	_	-	_	-	_	μs
Setup time of stop condition	tsu: sto	$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.$	$2.7~V \leq EV_{DD} \leq 5.5~V$			_		—		-	_	μs
Bus-free time	t BUF	$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.$	5 V	0.5		_		-		_	_	μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of the DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows. Fast mode plus: C_b = 120 pF, R_b = 1.1 k Ω

IICA serial transfer timing



Remark n = 0, 1

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-)= AV _{REFM}
ANI0 to ANI3	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI22	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$		1.2	±3.5	LSB
		AV _{REFP} = V _{DD} Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 and ANI3	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
		10-bit resolution Target pin: Internal reference voltage,	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	3.5625		39	μs
		and temperature sensor output voltage	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$1.8 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±0.25	%FSR
		AVREFP = VDD Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			±0.50	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$1.8 V \le AVREFP \le 5.5 V$		±0.25	%FSR	
		AVREFP = VDD Note 3	$1.6 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}^{\text{Note 4}}$			±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$	3.5625 39 17 39 ±0.25 4 ±0.50 ±0.25 4 ±0.50 ±0.50 ±0.50 ±0.50 ±1.5	LSB		
		AVREFP = VDD Note 3	$1.6 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±1.5	LSB
		AVREFP = VDD Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$			±2.0	LSB
Analog input voltage	VAIN	ANI2 and ANI3		0		AVREFP	V
		Internal reference voltage $(1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$		V _{BGR} Note 5			V
		Temperature sensor output voltage $(1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$		VT	MPS25 Not	ie 5	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3.	When AVREFP < VDD, the MAX. values are as follows.								
	Overall error:	Add ±1.0 LSB to the MAX. value when AVREFP = VDD.							
	Zero-scale error/Full-scale error:	Add ±0.05%FSR to the MAX. value when AVREFP = VDD.							
	Integral linearity error/ Differential linearity error:	Add ±0.5 LSB to the MAX. value when AVREFP = VDD.							
Note 4.	Values when the conversion time is set to 57 μ s	(min.) and 95 μs (max.).							

Note 5. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution $EV_{DD} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$		1.2	±5.0	LSB
			$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$ Note 5		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target ANI pin: ANI16 to ANI22	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution $EV_{DD} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±0.35	%FSR
			$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$ Note 5			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$		±0.35	%FSR	
		$EV_{DD} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 5}}$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±3.5	LSB
		$EV_{DD} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.6 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$ Note 5			±6.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±2.0	LSB
		$EV_{DD} \le AV_{REFP} = V_{DD}$ Notes 3, 4	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$ Note 5			±2.5	LSB
Analog input voltage	Vain	ANI16 to ANI22		0		AVREFP and EVDD	V

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD \le AVREFP < VDD$, the MAX. values are as follows.

Overall error:	Add ±1.0 LSB to the MAX. value when AVREFP = VDD.
Zero-scale error/Full-scale error:	Add ±0.05%FSR to the MAX. value when AVREFP = VDD.
Integral linearity error/ Differential linearity error:	Add ±0.5 LSB to the MAX. value when AVREFP = VDD.
When AVREFP < EVDD \leq VDD, the MAX. values an	e as follows.
Overall error:	Add ±4.0 LSB to the MAX. value when AVREFP = VDD.
Zero-scale error/Full-scale error:	Add ±0.20%FSR to the MAX. value when AVREFP = VDD.
Integral linearity error/ Differential linearity error:	Add ±2.0 LSB to the MAX. value when AVREFP = VDD.
	Zero-scale error/Full-scale error: Integral linearity error/ Differential linearity error: When AVREFP < $EVDD \le VDD$, the MAX. values ar Overall error: Zero-scale error/Full-scale error:

Note 5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3		1.2	±10.5	LSB
Conversion time	tCONV	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI3, ANI16 to ANI22	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ ± 0.60	±0.60	%FSR		
			$1.6~V \leq V_{DD} \leq 5.5~V~Note~3$			±0.85	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Note 1		$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}^{\text{N}}$	$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±2.5	LSB
Analog input voltage	VAIN	ANI0 to ANI3		0		Vdd	V
		ANI16 to ANI22		0		EVDD	V
		Internal reference voltage (1.8 V \leq VDD \leq 5.5 V)		VBGR Note 4			V
		Temperature sensor output voltage (1.8 V \leq VDD \leq 5.5 V)		۲V	VTMPS25 Note 4		

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 and ANI3, ANI16 to ANI22

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, 1.6 V \leq EVDD \leq VDD, Vss = 0 V, Reference voltage (+) = VBGR ^{Note 3}, Reference voltage (-) = AVREFM = 0 V ^{Note 4})

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv		17		39	μs
Zero-scale error Notes 1, 2	Ezs				±0.60	% FSR
Integral linearity error Note 1	ILE				±2.0	LSB
Differential linearity error Note 1	DLE				±1.0	LSB
Analog input voltage	VAIN		0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.



2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp	$2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	5			μs
		$1.8 \text{ V} \le \text{V}_{\text{DD}} < 2.4 \text{ V}$	10			μs

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, Vss = 0 V)

2.6.3 D/A converter (channel 1)

(TA = -40 to +85°C, 1.6 V \leq EVss \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8	bit	
Overall error	AINL	Rload = 4 M Ω 1.8 V \leq VDD \leq 5.5 V				±2.5	LSB
		Rload = 8 M Ω	$1.8~V \le V_{DD} \le 5.5~V$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7~V \leq V_{DD} \leq 5.5~V$			3	μs
			$1.6 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$			6	μs



2.6.4 Comparator

(Comparator 0: TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)	
(Comparator 1: TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)	

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	VIREF0	IVREF0 pin	0		VDD - 1.4 Note 1	V	
	VIREF1	REF1 IVREF1 pin		1.4 Note 1		Vdd	V
	VICMP	IVCMP0 pin		-0.3		VDD + 0.3	V
		IVCMP1 pin		-0.3		EVDD + 0.3	V
- 1 /	V _{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	μs	
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3		μs
			Comparator low-speed mode, window mode		4		μs
Operation stabilization wait time	tсмр		·	100			μs
Reference voltage declination in channel 0 of internal DAC ^{Note 2}	⊿VIDAC					± 2.5	LSB

Note 1. In window mode, make sure that VREF1 - VREF0 \ge 0.2 V.

Note 2. Only in CMP0



2.6.5 PGA

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA				±10	mV	
Input voltage range	Vipga			0		0.9 × V₀₀/Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{\text{DD}}$			V
	VIOLPGA					$0.07 \times V_{\text{DD}}$	V
Gain error		x4, x8				±1	%
		x16				±1.5	%
		x32				±2	%
Slew rate	SRrpga	Rising When VIN = 0.1V⊳⊳/gain to 0.9V⊳⊳/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
		10 to 90% of output	$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
		voltage amplitude	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
	SRfpga	Falling When VIN= 0.1Vbb/gain to 0.9Vbb/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			
		90 to 10% of output	$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
vo	voltage amplitude	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5				
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time ^{Note}		x16, x32				10	μs

(TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).



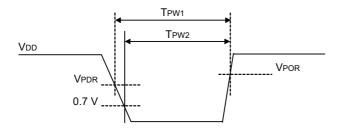
2.6.6 POR circuit characteristics

•						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	The power supply voltage is rising.	1.47	1.51	1.55	V
	VPDR	The power supply voltage is falling. Note 1	1.46	1.50	1.54	V
Minimum pulse width Note 2	TPW1	Other than STOP/SUB HALT/SUB RUN	300			μs
	TPW2	STOP/SUB HALT/SUB RUN	300			μs

(TA = -40 to +85°C, Vss = 0 V)

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.

Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.7 LVD circuit characteristics

(1) LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +85°C.	$\textbf{VPDR} \leq \textbf{EVDD} \leq \textbf{VDD} \leq \textbf{VD} = $	5.5 V. Vss = 0 V)
(

Pa	arameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	VLVD0	The power supply voltage is rising.	3.98	4.06	4.14	V
			The power supply voltage is falling.	3.90	3.98	4.06	V
		VLVD1	The power supply voltage is rising.	3.68	3.75	3.82	V
			The power supply voltage is falling.	3.60	3.67	3.74	V
		VLVD2	The power supply voltage is rising.	3.07	3.13	3.19	V
			The power supply voltage is falling.	3.00	3.06	3.12	V
		VLVD3	The power supply voltage is rising.	2.96	3.02	3.08	V
			The power supply voltage is falling.	2.90	2.96	3.02	V
		VLVD4	The power supply voltage is rising.	2.86	2.92	2.97	V
			The power supply voltage is falling.	2.80	2.86	2.91	V
		VLVD5	The power supply voltage is rising.	2.76	2.81	2.87	V
			The power supply voltage is falling.	2.70	2.75	2.81	V
		VLVD6	The power supply voltage is rising.	2.66	2.71	2.76	V
			The power supply voltage is falling.	2.60	2.65	2.70	V
		VLVD7	The power supply voltage is rising.	2.56	2.61	2.66	V
			The power supply voltage is falling.	2.50	2.55	2.60	V
		VLVD8	The power supply voltage is rising.	2.45	2.50	2.55	V
			The power supply voltage is falling.	2.40	2.45	2.50	V
		VLVD9	The power supply voltage is rising.	2.05	2.09	2.13	V
			The power supply voltage is falling.	2.00	2.04	2.08	V
		VLVD10	The power supply voltage is rising.	1.94	1.98	2.02	V
			The power supply voltage is falling.	1.90	1.94	1.98	V
		VLVD11	The power supply voltage is rising.	1.84	1.88	1.91	V
			The power supply voltage is falling.	1.80	1.84	1.87	V
		VLVD12	The power supply voltage is rising.	1.74	1.77	1.81	V
			The power supply voltage is falling.	1.70	1.73	1.77	V
		VLVD13	The power supply voltage is rising.	1.64	1.67	1.70	V
			The power supply voltage is falling.	1.60	1.63	1.66	V
Minimum pulse wid	th	tLW		300			μs
Detection delay tim	e					300	μs

(2) LVD Detection Voltage of Interrupt & Reset Mode

Parameter	Symbol	Conditions				TYP.	MAX.	Unit
Interrupt and	VLVDA0	VPOC0,	VPOC1, VPOC2 = 0, 0, 0, f	alling reset voltage	1.60	1.63	1.66	V
reset mode	VLVDA1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC0,	VPOC1, VPOC2 = 0, 0, 1, f	alling reset voltage	1.80	1.84	1.87	V
	VLVDB1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC0,	VPOC1, VPOC2 = 0, 1, 0, f	DC1, VPOC2 = 0, 1, 0, falling reset voltage		2.45	2.50	V
	VLVDC1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC0,	VPOC1, VPOC2 = 0, 1, 1, f	alling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

(TA = -40 to +85°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

2.6.8 Power supply voltage rising slope characteristics

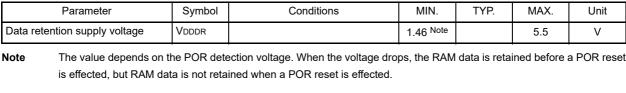
(TA = -40 to +85°C, Vss = 0 V)

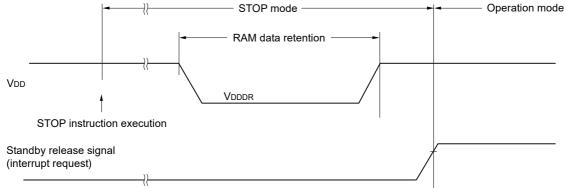
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.



2.7 RAM Data Retention Characteristics





2.8 Flash Memory Programming Characteristics

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditi	MIN.	TYP.	MAX.	Unit	
System clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1		24	MHz	
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	TA = 85°C	100,000			
		Retained for 20 years	TA = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.



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2.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

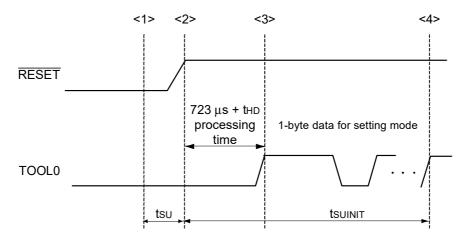
2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified ^{Note 1}	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) ^{Notes 1, 2}	thd	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μ s).



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.
 - tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
 - tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)



3. ELECTRICAL SPECIFICATIONS (TA = -40 to +105°C)

This chapter describes the following electrical specifications. Target products G: Industrial applications (TA = -40 to +105°C) R5F105xxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G11 User's Manual.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.
- Caution 4. When operating temperature exceeds 85°C, only HS (high-speed main) mode can be used as the flash operation mode. Regulator mode should be used with the normal setting (MCSEL = 0).
- Caution 5. The EVDD pin is not present on products with 24 or less pins. Accordingly, replace EVDD with VDD and the voltage condition 1.6 ≤ EVDD ≤ VDD ≤ 5.5 V with 1.6 ≤ VDD ≤ 5.5 V.
- **Remark** When the products "G: Industrial applications" is used in the range of TA = -40 to +85°C, see 2. **ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)**.



Fields of application	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	TA = -40 to +105°C
Operating mode Operating Voltage Range	$\begin{array}{l} \text{HS (High-speed main) mode:} \\ 2.7 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V} @ 1 \ \text{MHz to } 24 \ \text{MHz} \\ 2.4 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V} @ 1 \ \text{MHz to } 16 \ \text{MHz} \\ \text{LS (Low-speed main) mode:} \\ 1.8 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V} @ 1 \ \text{MHz to } 8 \ \text{MHz} \\ \text{LV (Low-voltage main) mode:} \\ 1.8 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V} @ 1 \ \text{MHz to } 4 \ \text{MHz} \\ \end{array}$	Only in HS (High-speed main) mode: 2.7 V \leq VDD \leq 5.5 V @ 1 MHz to 24 MHz 2.4 V \leq VDD \leq 5.5 V @ 1 MHz to 16 MHz
High-speed on-chip oscillator clock to an accuracy	$\begin{array}{l} 1.8 \ V \leq V \text{DD} \leq 5.5 \ V: \\ \pm 1.0\% \ @ \ Ta = -20 \ to \ +85^{\circ}\text{C} \\ \pm 1.5\% \ @ \ Ta = -40 \ to \ -20^{\circ}\text{C} \\ 1.6 \ V \leq V \text{DD} < 1.8 \ V: \\ \pm 5.0\% \ @ \ Ta = -20 \ to \ +85^{\circ}\text{C} \\ \pm 5.5\% \ @ \ Ta = -40 \ to \ -20^{\circ}\text{C} \end{array}$	$2.4 V \le V_{DD} \le 5.5 V$: ±2.0% @ TA = +85 to +105°C ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C
Serial array unit	UART Simplified SPI (CSI): fcLk/2 (12 Mbps are supported), fcLk/4 Simplified I ² C	UART Simplified SPI (CSI): fcLk/4 Simplified I ² C
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fast mode
Voltage Detector	• Rising: 1.67 V to 4.06 V (14 levels) • Falling: 1.63 V to 3.98 V (14 levels)	Rising: 2.61 V to 4.06 V (8 levels) Falling: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics for "G: Industrial applications" differ from those for "A: Consumer applications" when the product is in use in an ambient temperature over 85°C. For details, see **3.1** to **3.10** in the following pages.



3.1 Absolute Maximum Ratings

				(1/2
Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD		-0.5 to +6.5	V
	AVREFP		0.3 to V _{DD} + 0.3 ^{Note 2}	V
	AVREFM		-0.3 to V _{DD} + 0.3 Note 2 and AVREFM ≤ AVREFP	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	VI1	P00, P01, P30 to P33, P40, and P51 to P56	-0.3 to EV _{DD} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	Vı2	P20 to P23, P121, P122, P125, P137, EXCLK, RESET	-0.3 to V _{DD} + 0.3 ^{Note 2}	V
Output voltage	Vo1	P00, P01, P30 to P33, P40, and P51 to P56	-0.3 to EV _{DD} + 0.3 and -0.3 to V _{DD} + 0.3 ^{Note 2}	V
	Vo2	P20 to P23	-0.3 to VDD + 0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI22	-0.3 to EV _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 ^{Notes 2, 3}	V
	Vai2	ANI0 to ANI3	-0.3 to VDD + 0.3 and -0.3 to AVREF(+) + 0.3 Notes 2, 3	V

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. AVREF (+): + side reference voltage of the A/D converter.

Remark 3. Vss: Reference voltage



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Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00, P01, P30 to P33, P40, P51 to P56	-40	mA
		Total of all pins	P00, P01, P40	-70	mA
		-170 mA	P30 to P33, P51 to P56	-100	mA
	Іон2	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low IOL	IOL1	Per pin	P00, P01, P30 to P33, P40, P51 to P56	40	mA
		Total of all pins	P00, P01, P40	70	mA
		170 mA	P30 to P33, P51 to P56	100	mA
	IOL2	Per pin	P20 to P23	1	mA
		Total of all pins		4	mA
Operating ambient	ТА	In normal operation mode		-40 to +105	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.2 Oscillator Characteristics

3.2.1 X1 characteristics

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4~\text{V} \leq \text{Vdd} < 2.7~\text{V}$	1.0		16.0	

Note Indicates only permissible oscillator frequency ranges. Refer to **3.4 AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Remark When using the X1 oscillator, refer to 6.4 System Clock Oscillator in the RL78/G11 User's Manual.

3.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1		24	MHz
		$2.4 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	1		16	
High-speed on-chip oscillator clock frequency accuracy		TA = +85°C to +105°C	-2		2	%
		TA = -20°C to +85°C	-1		1	%
		TA = -40°C to -20°C	-1.5		1.5	%
Middle-speed on-chip oscillator oscillation frequency Note 2	fім		1		4	MHz
Middle-speed on-chip oscillator oscillation frequency accuracy			-12		+12	%
Temperature drift of Middle-speed on-chip oscillator oscillation frequency accuracy	DIMT			0.008		%/°C
Voltage drift of Middle-speed on-chip oscillator oscillation frequency accuracy	Ы₩∨	TA = 25°C		0.02		%/V
Low-speed on-chip oscillator clock frequency Note 2	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to 3.4 AC Characteristics for instruction execution time.



Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

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3.3 DC Characteristics

3.3.1 Pin characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high IOH1 Note 1	Іон1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				-3.0 Note 2	mA
		Total of P00, P01, and P40	$4.0~V \le EV_{DD} \le 5.5~V$			-12.5	mA
		2	$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$			-10.0	mA
			$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			-5.0	mA
		Total of P30 to P33, and P51 to P56	$4.0~V \le EV_{DD} \le 5.5~V$			-30.0	mA
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			-19.0	mA
			$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				-42.5	mA
	Іон2	Per pin for P20 to P23				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$			-0.4	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IOH × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoH = -10.0 mA Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) \approx -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Io Note 1	IOL1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				8.5 Note 2	mA
		Total of P00, P01, and P40	$4.0~V \leq EV_{DD} \leq 5.5~V$			36.0	mA
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			15.0	mA
			$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			9.0	mA
		Total of P30 to P33, and P51 to P56	$4.0~V \leq EV_{DD} \leq 5.5~V$			40.0	mA
		(When duty \leq 70% ^{Note 3})	$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			35.0	mA
			$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			20.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				76.0	mA
	IOL2	Per pin for P20 to P23				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$			1.6	mA

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) \approx 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Symbol Conditions			TYP.	MAX.	Unit
Input voltage, high	VIH1	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0.8 EVDD		EVDD	V
	VIH2	P00, P30 to P32, P40, P51 to P56	TTL mode 4.0 V \leq EV _{DD} \leq 5.5 V	2.2		EVdd	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	2.0		EVDD	V
			TTL mode 2.4 V ≤ EV _{DD} < 3.3 V	1.5		EVDD	V
	Vінз	P20 to P23 (digital input)	•	0.7 Vdd		Vdd	V
	VIH4	P121, P122, P125, P137, EXCL	K, RESET	0.8 Vdd		Vdd	V
Input voltage, low	VIL1	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0		0.2 EVDD	V
	VIL2	P00, P30 to P32, P40, P51 to P56	TTL mode $4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$	0		0.8	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	0		0.5	V
			TTL mode 2.4 V ≤ EV _{DD} < 3.3 V	0		0.32	V
	VIH3	P20 to P23 (digital input)	1	0		0.3 Vdd	V
	VIH4	P121, P122, P125, P137, EXCL	(, RESET	0		0.2 Vdd	V

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}\text{DD} \le \text{V}\text{DD} \le 5.5 \text{ V}, \text{V}\text{ss} = 0 \text{ V})$

The maximum value of VIH of pins P00, P01, P20, P30 to P33, P40 and P51 to P56 is VDD or EVDD, even in the N-ch Caution open-drain mode.

(P20: VDD

P00, P01, P30 to P33, P40, P51 to P56: EVDD)



Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)							(4/5)
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00, P01, P30 to P33, P40, and P51 to P56	4.0 V ≤ EV _{DD} ≤ 5.5 V, Іон = -3.0 mA	EVDD - 0.7			V
			2.7 V ≤ EVDD ≤ 5.5 V, Іон = -2.0 mA	EVDD - 0.6			V
			2.4 V ≤ EVDD ≤ 5.5 V Іон = -1.5 mA	EVDD - 0.5			V
	Voh2	P20 to P23	2.4 V ≤ Vdd ≤ 5.5 V, Іон = -100 µА	Vdd - 0.5			V
Output voltage, low	VOL1	P00, P01, P30 to P33, P40, and P51 to P56	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ $\text{IOL} = 8.5 \text{ mA}$			0.7	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ Iol = 3.0 mA			0.6	V
			$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ IoL = 1.5 mA			0.4	V
			$2.4 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$ IoL = 0.6 mA			0.4	V
	Vol2	P20 to P23	$\begin{array}{l} 2.4 \ \text{V} \leq \text{Vdd} \leq 5.5 \ \text{V}, \\ \text{Iol} = 400 \ \mu\text{A} \end{array}$			0.4	V

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode. Caution

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(TA = -40 to +10	05°C, 2.4	$V \le EV$ DD $\le V$ DD $\le 5.5 V$, Vss =	0 V)					(5/5)
Items	Symbol	Conc	litions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00, P01, P30 to P33, P40, and P51 to P56	VI = EVDD				1	μA
	ILIH2	P20 to P23, P125, P137, RESET	VI = VDD				1	μA
	Ілнз	P121, P122, X1, X2, EXCLK	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	ILIL1	P00, P01, P30 to P33, P40, and P51 to P56	VI = VSS				-1	μA
	ILIL2	P20 to P23, P125, P137, RESET	VI = Vss				-1	μA
	Ilil3	P121, P122, X1, X2, EXCLK	VI = VSS	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P00, P01, P30 to P33, P40, P51 to P56, P125	VI = Vss, I	n input port	10	20	100	kΩ

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins. Remark



3.3.2 Supply current characteristics

(Т/	Δ = -40 to +105°C	2.4 V < FVpp <	< VDD < 5.5 V	Vss = 0 V
(' '		,		, • • • • • • • • • • • •

Parameter	Symbol				Conditions			MIN.	TYP.	MAX.	Unit
Supply current	IDD1	Operating	Basic	HS (high-speed main)	fHOCO = 48 MHz ^{Note 3}	V _{DD} = 5.0 V			1.7		mA
Note 1		mode	operation	mode	fiH = 24 MHz Note 3	fiH = 24 MHz Note 3 VDD = 3.0 V			1.7		
					fHOCO = 24 MHz ^{Note 3}	V _{DD} = 5.0 V			1.4		
					fiH = 24 MHz Note 3	V _{DD} = 3.0 V			1.4		
			Normal	HS (high-speed main)	fHOCO = 48 MHz ^{Note 3}	V _{DD} = 5.0 V			3.5	7.3	mA
			operation	mode	fiH = 24 MHz Note 3	V _{DD} = 3.0 V			3.5	7.3	
					fHOCO = 24 MHz ^{Note 3}	V _{DD} = 5.0 V			3.2	6.7	
					fiH = 24 MHz Note 3	V _{DD} = 3.0 V			3.2	6.7	
					fHOCO = 16 MHz ^{Note 3}	V _{DD} = 5.0 V			2.4	4.9	
					fiH = 16 MHz Note 3	V _{DD} = 3.0 V			2.4	4.9	
			Normal	HS (high-speed main)	ain) $f_{MX} = 20 \text{ MHz Note 2} V_{DD}$	V _{DD} = 5.0 V	Square wave input		2.7	5.7	mA
			operation	mode			Resonator connection		2.8	5.8	
						V _{DD} = 3.0 V	Square wave input		2.7	5.7	
							Resonator connection		2.8	5.8	
					f _{MX} = 10 MHz Note 2	V _{DD} = 5.0 V	Square wave input		1.8	3.4	
							Resonator connection		1.9	3.5	
						V _{DD} = 3.0 V	Square wave input		1.8	3.4	
							Resonator connection		1.9	3.5	
			Normal operation	Subsystem clock operation	fi∟ = 15 kHz, T₄ = - 40°C ^{Note 4}				1.8	5.9	μA
					fi∟ = 15 kHz, T _A =				1.9	5.9	
					+25°C Note 4						
					fi∟ = 15 kHz, T _A = +85°C ^{Note 4}				2.3	8.7	
					f⊫ = 15 kHz, T _A = +105°C ^{Note 4}				3.0	20.9	

Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main) modes.

• The currents in the "TYP." column do not include the operating currents of the peripheral modules.

• The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.

Note 3. When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.

Note 4. When the high-speed system clock, high-speed on-chip oscillator clock and middle-speed on-chip oscillator clock are stopped.

Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. file: High-speed on-chip oscillator clock frequency (24 MHz max.)

Remark 3. fim: Middle-speed on-chip oscillator clock frequency (4 MHz max.)

Remark 4. fiL: Low-speed on-chip oscillator clock frequency

Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)

Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



(1/3)

(2/3)

17 40 (0.100	0, 2		3 v , v 33 – 0 v)						(2/5
Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT	HS (high-speed main) mode	fHOCO = 48 MHz Note 3	V _{DD} = 5.0 V			0.59	3.45	mA
lote 1	Note 2	mode		fiH = 24 MHz Note 4	V _{DD} = 3.0 V			0.59	3.45	
				fHOCO = 24 MHz Note 3	V _{DD} = 5.0 V			0.41	2.85	
				fiH = 16 MHz Note 4	V _{DD} = 3.0 V			0.41	2.85	
				fHOCO = 16 MHz Note 3	V _{DD} = 5.0 V			0.39	2.08	
				fiH = 16 MHz Note 4	V _{DD} = 3.0 V			0.39	2.08	
			HS (high-speed main) mode	f _{MX} = 20 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.20	2.45	mA
				Resonator connection		0.40	2.57			
					V _{DD} = 3.0 V	Square wave input		0.20	2.45	
						Resonator connection		0.40	2.57	
				f _{MX} = 10 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.15	1.28	
						Resonator connection		0.30	1.36	
					V _{DD} = 3.0 V	Square wave input		0.15	1.28	
						Resonator connection		0.30	1.36	
			Subsystem clock operation	fi∟ = 15 kHz, T₄ = -40°C	Note 5			0.48	1.22	μA
				fı∟ = 15 kHz, T _A = +25°0	Note 5			0.55	1.22	
				fı∟ = 15 kHz, T₄= +85°0	Note 5			0.80	3.30	
				fil = 15 kHz, TA = +105	°C Note 5			2.00	17.3	

(TA = -40 to +105°C, 2.4 V \leq EVDD $\leq~$ VDD $\leq~$ 5.5 V, Vss = 0 V)

Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main) modes.

• The currents in the "TYP." column do not include the operating currents of the peripheral modules.

• The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

Note 2. When the HALT instruction is executed in the flash memory.

Note 3. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and low-speed on-chip oscillator clock are stopped.

- **Note 4.** When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 5.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and high-speed system clock are stopped.

Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- Remark 2. fill: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 3. fim: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fiL: Low-speed on-chip oscillator clock frequency

Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)

Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(TA = -40 to +10)5°C, 2.4 ∖	$I \leq EVDD \leq VDD$	0 ≤ 5.5 V, Vss = 0 V)				(3/3)	
Parameter	Symbol		Conditions MIN. TYP. MA					
Supply current	IDD3	STOP mode	TA = -40°C		0.19	0.51	μA	
Note 1		Note 2	TA = +25°C		0.25	0.51		
			TA = +50°C		0.28	1.10		
			TA = +70°C		0.38	1.90		
			TA = +85°C		0.60	3.30		
			TA = +105°C		1.5	17.0		

Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when Note 2. operating the subsystem clock in HALT mode.



Peripheral Functions (Common to all products)

(TA = -40 to +105°C, 2.4 V \leq EVDD $\leq~$ VDD $\leq~$ 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.22		μA
12-bit interval timer operating current	ITMKA Notes 1, 3, 4	fiL = 15 kHz fmain stopped (per unit)			0.02		μΑ
8-bit interval timer operating current	Ітмт	fı∟ = 15 kHz	8-bit counter mode × 2-channel operation		0.04		μA
Notes 1, 9		fmain stopped (per unit)	16-bit counter mode operation		0.03		μA
Watchdog timer operating current	I _{WDT} Notes 1, 3, 5	fiL = 15 kHz fмаin stopped (per unit)			0.22		μΑ
A/D converter operating current	J _{ADC} Notes 1, 6	During maximum-speed	Normal mode, AV _{VREFP} = V _{DD} = 5.0 V		1.3	1.7	mA
		conversion	Low voltage mode, AV_VREFP = V_{DD} = 3.0 V		0.5	0.7	mA
Internal reference voltage (1.45 V) current Notes 1, 10	IADREF				85.0		μΑ
Temperature sensor operating current	ITMPS Note 1				85.0		μA
D/A converter operating current	IDAC Note 1	Per channel				1.5	mA
PGA operating current	IPGA Notes 1, 2				480	700	μA
Comparator operating current	ICMP Note 8	V _{DD} = 5.0 V, Regulator output voltage	Comparator high-speed mode Window mode		12.5		μΑ
		= 2.1 V	Comparator low-speed mode Window mode		3.0		
			Comparator high-speed mode Standard mode		6.5		
			Comparator low-speed mode Standard mode		1.9		
		V _{DD} = 5.0 V, Regulator output voltage	Comparator high-speed mode Window mode		8.0		
		= 1.8 V	Comparator low-speed mode Window mode		2.2		
			Comparator high-speed mode Standard mode		4.0		
			Comparator low-speed mode Standard mode		1.3		
LVD operating current	ILVD Notes 1, 7				0.10		μA
Self-programming operating current	IFSP Notes 1, 12				2.0	12.20	mA
BGO current	IBGO Notes 1, 11				2.0	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	Mode transition Note 13		0.50	1.10	mA
		fih = 24 MHz, AVREFP = V _{DD} = 3.0 V	The A/D conversion operations are performed		1.20	2.04	mA
		Simplified SPI (CSI)/UART	operation fiH = 24 MHz		0.70	1.54	mA
	ISNOZM Note 1	ADC operation	Mode transition Note 13		0.05	0.13	mA
		fim = 4 MHz, AVREFP = V _{DD} = 3.0 V	The A/D conversion operations are performed		0.67	0.84	mA
		Simplified SPI (CSI) operate	tion, fim = 4 MHz	1	0.06	0.15	mA

(Notes and Remarks are listed on the next page.)



Note 1. Current flowing to VDD.

- Note 2. Operable range is 2.7 to 5.5 V.
- **Note 3.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and high-speed system clock are stopped.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- **Note 8.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 9. Current flowing only to the 8-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 8-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- **Note 10.** Current consumed by generating the internal reference voltage (1.45 V).
- Note 11. Current flowing during programming of the data flash.
- Note 12. Current flowing during self-programming.
- Note 13. For transition time to the SNOOZE mode, see 24.3.3 SNOOZE mode in the RL78/G11 User's Manual.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fcLK: CPU/peripheral hardware clock frequency
- **Remark 3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



3.4 AC Characteristics

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Тсү	Main system clock	HS (high-speed main)	$2.7~V \leq V\text{DD} \leq 5.5~V$	0.04167		1	μs
(minimum instruction		(fMAIN) operation	mode	$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μs
execution time)		Subsystem clock (fsub) operation	fiL	$2.4 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$		66.7		μs
		In the self-	HS (high-speed main)	$2.7~V \leq V \text{DD} \leq 5.5~V$	0.04167		1	μs
		programming mode	mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	0.0625		1	μs
External system	fEX	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	1		1		20	MHz
clock frequency		$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	/		1		16	MHz
External system	texн,	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	/		24			ns
clock input high-/low- level width	texL	$2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V}$	/		30			ns
TI00 to TI03 input high-/low-level width	ttih, ttil ^{Note 1}				1/fмск + 10			ns
TO00 to TO03,	fтo	TO00 to TO03,	HS (high-speed main)	$4.0~V \le EV_{DD} \le 5.5~V$			12	MHz
TKBO0, and TKBO1		TKBO0, and	mode	$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			8	1
output frequency Note 2		ТКВО1		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			4	
		(in the case of						
		output from port						
		pins other than						
		P20)						
		TKBO1	HS (high-speed main)	$4.0~V \leq V_{DD} \leq 5.5~V$			1.5	MHz
		(in the case of	mode	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$			1.2	
		output from P20)		$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$			1	
PCLBUZ0, PCLBUZ1	f PCL	HS (high-speed ma	ain) mode	$4.0~V \leq EV_{DD} \leq 5.5~V$			16	MHz
output frequency				$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}$			8	
				$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 2.7 \text{ V}$			4	
Interrupt input high-	tinth,	INTP0 to INTP2, IN	ITP9	$2.4~V \leq V \text{DD} \leq 5.5~V$	1			μs
/low-level width	tintl	INTP3 to INTP8, IN	ITP10, INTP11	$2.4~V \leq EV_{DD} \leq 5.5~V$	1			
Key interrupt input low-level width	tкr	KR0 to KR7		$2.4 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	250			ns
RESET low-level width	tRSL				10			μs

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

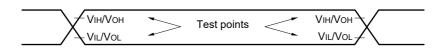
 $\label{eq:Note1.} \begin{array}{ll} \mbox{Following conditions must be satisfied on low level interface of EVDD < VDD.} \\ 2.4 \ \mbox{V} \leq \mbox{EVDD} \leq 2.7 \ \mbox{V: MIN.125 ns} \end{array}$

Note 2. When duty is 50%.

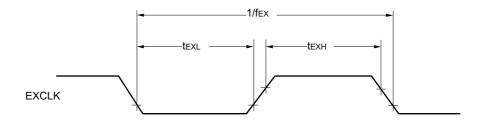
Remark fMCK: Timer array unit operation clock frequency (Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))



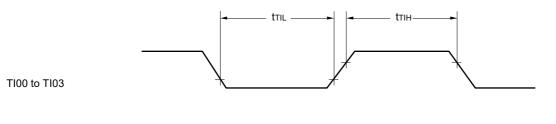
AC Timing Test Points

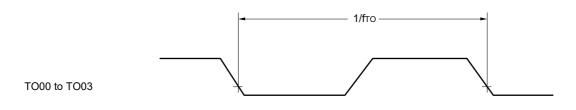


External System Clock Timing

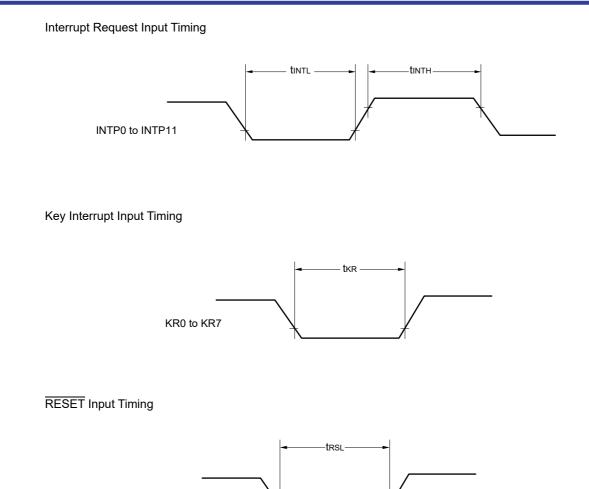


TI/TO Timing









RESET



3.5 Peripheral Functions Characteristics

AC Timing Test Points

Viн/Voн VIH/VOH Test points VIL/VOL . VIL/VOL



3.5.1 Serial array unit

(1) during communication at same potential (UART mode) When P01, P30, P31 and P54 are used as TxDq pin

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Svmbol	Conditions	HS (high-sp	Unit	
Falameter Symbol		Conditions	MIN.	MAX.	Onit
Transfer rate		Theoretical value of the maximum transfer		fмск/12 ^{Notes 1, 2}	bps
		rate fмск = fclк = 24 MHz		2.0	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2.The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:
HS (high-speed main) mode:
 $2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 2.7 \text{ V}$: MAX. 1.3 Mbps

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

When P20 is used as TxD1 pin

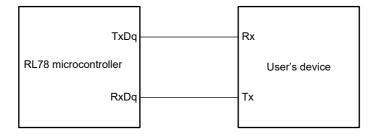
(TA = -40 to +105°C, 2.4 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
Falameter	Symbol	Conditions	MIN.	MAX.	Offit
Transfer rate		$4.0 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$		fмск/16 ^{Note}	bps
		Theoretical value of the maximum transfer rate fмск = fcLк = 24 MHz		1.5	Mbps
		$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$		fмск/20 ^{Note}	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK = 24 MHz		1.2	Mbps
		$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$		fмск/16 ^{Note}	bps
		Theoretical value of the maximum transfer rate fмск = fcLк = 16 MHz		1.0	Mbps

Note Transfer rate in the SNOOZE mode is 4800 bps only. When fHoco = 48 MHz, SNOOZE mode is not supported.



UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3 and 5)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03)



(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

When P01, P32, P53, P54 and P56 are used as SOmn pins

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	C	Conditions	HS (high-spee	ed main) Mode	Unit
Falaniciel	Symbol		Conditions		MAX.	Unit
SCKp cycle time	tксү1	tĸcy1 ≥ 4/fcLĸ	$2.7~V \leq EV_{DD} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD} \leq 5.5~V$	500		ns
SCKp high-/low-level width	tĸнı, tĸ∟ı	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		tксү1/2 - 24		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}$		tксү1/2 - 36		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	tксү1/2 - 7 6		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	66		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V			ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5$	5.5 V	133		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi1			38		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF Note 4			50	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. fMck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



When P20 is used as SO10 pin

(TA = -40 to +105°C, 2.4 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions		HS (high-speed main) Mode		
Falameter	Symbol				MAX.	Unit	
SCKp cycle time	tксү1	tксү1 ≥ 4/fcLк	tkcy1 \ge 4/fclk 2.7 V \le VDD \le 5.5 V			ns	
			$2.4~V \leq V_{DD} \leq 5.5~V$	1200		ns	
SCKp high-/low-level width	tĸнı, tĸ∟ı	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.$	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$			ns	
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$	5 V	tксү1/2 - 36		ns	
		$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.$	5 V	tксү1/2 - 76		ns	
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.$	5 V	66		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		133		ns	
SIp hold time (from SCKp [↑]) Note 2	tksi1			38		ns	
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF Note 4			180	ns	

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 2. fMck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(1/2)

(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

When P01, P32, P53, P54 and P56 are used as SOmn pins $(T_{1} = 40.45, 125^{\circ}C_{1}, 2.4)$

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

HS (high-speed main) Mode Conditions Parameter Symbol Unit MAX. MIN 4.0 V ≤ EVDD ≤ 5.5 V fMCK > 20 MHz 16/fмск SCKp cycle time Note 4 tKCY2 ns fмск ≤ 20 MHz 12/fмск ns $2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}$ fмск > 16 MHz 16/fмск ns fмск ≤ 16 MHz 12/fмск ns $2.4~V \leq EV_{DD} < 2.7~V$ 12/fмск and 1000 ns SCKp high-/low-level width tkh2, tkl2 $4.0~V \leq EV_{\text{DD}} \leq 5.5~V$ tkcy2/2 - 14 ns tKH2, tKL2 $2.7~V \leq EV_{DD} < 4.0~V$ tkcy2/2 - 16 ns $2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 2.7 \text{ V}$ tkcy2/2 - 36 ns SIp setup time (to SCKp[↑]) Note 1 $2.7~V \leq EV_{\text{DD}} \leq 5.5~V$ 1/fмск + 40 tsik2 ns $2.4~\text{V} \leq \text{EV}_{\text{DD}} < 2.7~\text{V}$ 1/fмск + 60 ns 1/fмск + 62 SIp hold time (from SCKp¹) Note 1 tksi2 ns C = 30 pF Note 3 $2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$ 2/fмск + 66 Delay time from SCKp \downarrow to SOp output $^{Note\ 2}$ tkso2 ns $2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 2.7 \text{ V}$ 2/fмск + 113 ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. C is the load capacitance of the SOp output lines.

Note 4. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Sympol		Conditions	HS (high-speed	d main) Mode	Unit
Parameter	Symbol		Conditions	MIN.	MAX.	Unit
SSI00 setup time	tssik	DAPmn = 0	$2.7~V \leq V_{DD} \leq 3.6~V$	240		ns
			$2.4~\text{V} \leq \text{V}_\text{DD} < 2.7~\text{V}$	400		ns
		DAPmn = 1	$2.7~V \leq V_{DD} \leq 3.6~V$	1/fмск + 240		ns
			$2.4~\text{V} \leq \text{V}_{\text{DD}} < 2.7~\text{V}$	1/fмск + 400		ns
SSI00 hold time	tĸssi	DAPmn = 0	$2.7~V \leq V_{DD} \leq 3.6~V$	1/fмск + 240		ns
			$2.4~\text{V} \leq \text{V}_{\text{DD}} < 2.7~\text{V}$	1/fмск + 400		ns
		DAPmn = 1	$2.7~V \leq V_{DD} \leq 3.6~V$	240		ns
			$2.4~\text{V} \leq \text{V}_{\text{DD}} < 2.7~\text{V}$	400		ns

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5, 12)



When P20 is used as SO10 pin

(TA = -40 to +105°C, 2.4 V \leq EVDD = VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		
				MIN.	MAX.	Unit
SCKp cycle time ^{Note 4}	tксү2	$4.0 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	fмск > 20 MHz	20/fмск		ns
			fмск ≤ 20 MHz	18/fмск		ns
		$2.7 \text{ V} \leq \text{Vdd} < 4.0 \text{ V}$	fмск > 16 MHz	20/fMCK and 1000		ns
			fмск ≤ 16 MHz	18/fмск		ns
		$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$		18/fмск and 1200		ns
SCKp high-/low-level width	tkh2, tkl2	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2 - 14		ns
	tkh2, tkl2	$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$		tксү2/2 - 16		ns
		$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$		tkcy2/2 - 36		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsık2	$2.7~V \leq V_{DD} \leq 5.5~V$		1/fмск + 40		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output ^{Note 2}	tkso2	C = 30 pF Note 3	$2.7~V \leq V_{DD} \leq 5.5~V$		2/fмск + 190	ns
			$2.4~\text{V} \leq \text{V}_{\text{DD}} < 2.7~\text{V}$		2/fмск + 250	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. C is the load capacitance of the SOp output lines.

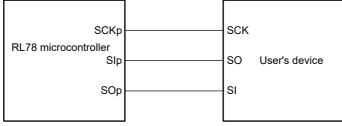
Note 4. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

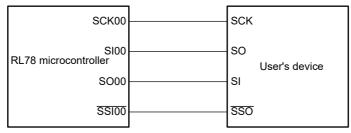
- **Remark 1.** p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



Simplified SPI (CSI) mode connection diagram (during communication at same potential)

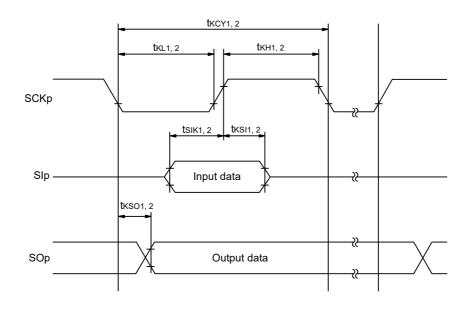


Simplified SPI (CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))

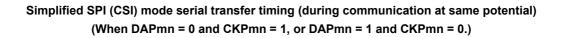


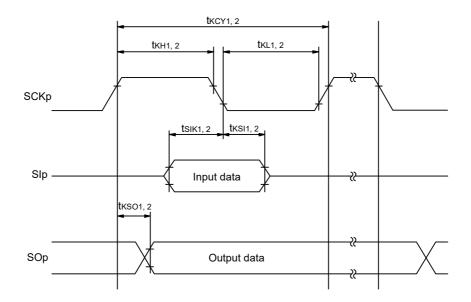
Remark p: CSI number (p = 00, 01, 10 and 11)





Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark 1. p: CSI number (p = 00, 01, 10 and 11) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03)

(4) During communication at same potential (simplified I²C mode)

Parameter	Symbol	Conditions	HS (high-speed	main) Mode	Unit
Parameter	Symbol	Conduons	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq EV_{DD} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ Rb} = 2.7 \mbox{ k}\Omega \end{array}$		400 Note 1	kHz
		$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{array}$		100 Note 1	kHz
Hold time when SCLr = "L"	t∟ow	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq \mbox{EV}_{\mbox{DD}} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1200		ns
		$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{array}$	4600		ns
Hold time when SCLr = "H"	tнigн	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq \mbox{EV}_{\mbox{DD}} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1200		ns
		$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{array}$	4600		ns
Data setup time (reception)	tsu: dat	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq \mbox{EV}_{\mbox{DD}} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	1/fмск + 220 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{array}$	1/fмск + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$\label{eq:linear} \begin{array}{l} 2.7 \mbox{ V} \leq \mbox{EV}_{\mbox{DD}} \leq 5.5 \mbox{ V}, \\ C_b = 50 \mbox{ pF}, \mbox{ R}_b = 2.7 \mbox{ k}\Omega \end{array}$	0	770	ns
		$\label{eq:linear} \begin{array}{l} 2.4 \ V \leq EV_{DD} \leq 5.5 \ V, \\ C_b = 100 \ pF, \ R_b = 3 \ k\Omega \end{array}$	0	1420	ns

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

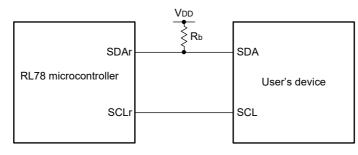
Note 1. The value must be equal to or less than fMCK/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

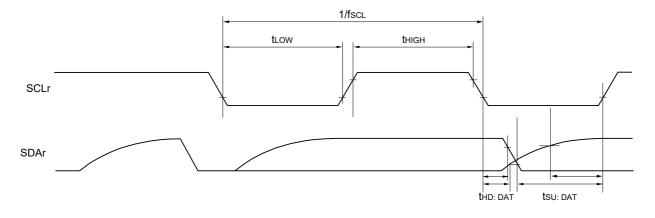
Caution Select the normal input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).



Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. $Rb[\Omega]$: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 01, 10 and 11), g: PIM number (g = 0, 3 and 5), h: POM number (h = 0, 3 and 5)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3), mn = 00 to 03)



(1/2)

(5) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (UART mode) (dedicated baud rate generator output)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

HS (high-speed main) Mode Parameter Symbol Conditions Unit MIN. MAX Transfer rate $4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V},$ fмск/12 Note 1 Reception bps $23V \le V_h \le 40V$ Theoretical value of the maximum transfer rate 2.0 Mbps fMCK = fCLK Note 3 $2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V},$ fMCK/12 Note 1 bps $2.3~V \leq V_b \leq 2.7~V$ Theoretical value of the maximum transfer rate 2.0 Mbps fMCK = fCLK Note 3 $2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 3.3 \text{ V},$ fMCK/12 Notes 1, 2 bps $1.6 V \le V_b \le 2.0 V$ Theoretical value of the maximum transfer rate 1.3 Mbps fMCK = fCLK Note 3

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with $EV_{DD} \ge Vb$.

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remark 1.** Vb[V]: Communication line voltage
- **Remark 2.** q: UART number (q = 0 and 1), g: PIM and POM numbers (g = 0, 2, 3, 5, 12)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

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(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Deservator	O maked			HS (high-	11-34	
Parameter	Symbol		Conditions	MIN.	MAX.	Unit
Transfer rate		Transmission	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k\Omega, V_b = 2.7 V		2.6 ^{Note 2}	Mbps
			$2.7 \text{ V} \le EV_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V}$		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 Note 4	Mbps
			$2.4 \text{ V} \le EV_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le V_{\text{b}} \le 2.0 \text{ V}$		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}\text{DD} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{V}\text{b} \le 4.0 \text{ V}$

mum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$

1

Baud rate error (theoretical value) =

Maxi

value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

1

- Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

 Note 3.
 The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.
 - Expression for calculating the transfer rate when 2.7 V \leq EVDD \leq 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times In (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 4.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

 $\label{eq:Note 5.} \qquad \text{Use it with } EV_{DD} \geq V_b.$



Note 6. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $2.4 \text{ V} \le \text{EV}\text{DD} < 3.3 \text{ V}$ and $1.6 \text{ V} \le \text{V}\text{b} \le 2.0 \text{ V}$

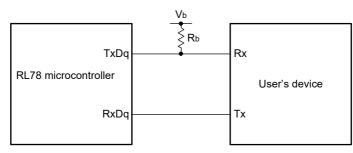
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times 100 [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

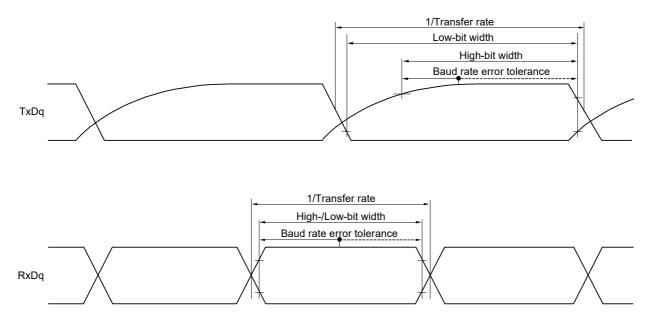
- **Note 7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



- **Remark 1.** Rb[Ω]: Communication line (TxDq) pull-up resistance, Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)

Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))



(1/2)

(6) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

HS (high-speed main) Mode Parameter Symbol Conditions Unit MIN. MAX. $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ SCKp cycle time tkCY1 tkcy1 ≥ 4/fclk 600 ns $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$ $2.7~V \leq EV_{DD} < 4.0~V, 2.3~V \leq V_b \leq 2.7~V,$ 1000 ns C_b = 30 pF, R_b = 2.7 k Ω $2.4~V \leq EV_{DD} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V,$ 2300 ns C_b = 30 pF, R_b = 5.5 k Ω SCKp high-level width tĸH1 $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ tkcy1/2 - 150 ns $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$ $2.7~\text{V} \leq EV_\text{DD} < 4.0~\text{V},\, 2.3~\text{V} \leq V_b \leq 2.7~\text{V},$ tkcy1/2 - 340 ns C_b = 30 pF, R_b = 2.7 k Ω $2.4~V \leq EV_{DD} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V,$ tkcy1/2 - 916 ns $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ SCKp low-level width tkcy1/2 - 24 tĸ∟1 $4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ ns $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$ $t_{KCY1/2} - 36$ $2.7 \text{ V} \le EV_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ ns $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ tkcy1/2 - 100 ns $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the page after the next page.)



(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol	Conditions		peed main) ode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; \text{V}, \; 2.7 \; \text{V} \leq V_b \leq 4.0 \; \text{V}, \\ C_b = 30 \; \text{pF}, \; \text{R}_b = 1.4 \; \text{k} \Omega \end{array}$	162		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	354		ns
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 3}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	958		ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1		38		ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq E V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$			ns
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \mbox{Note 3}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$			ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; \text{V}, \; 2.7 \; \text{V} \leq V_b \leq 4.0 \; \text{V}, \\ C_b = 30 \; \text{pF}, \; \text{R}_b = 1.4 \; \text{k}\Omega \end{array}$		200	ns
		$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		390	ns
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 3}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		966	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1		88		ns
		$\begin{array}{l} 2.7 \; V \leq E V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$			ns
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \mbox{Note 3}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	220		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksi1		38		ns
		$\begin{array}{l} 2.7 \; V \leq E V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$			
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 3}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$			ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		50	ns
		$\label{eq:VD} \begin{array}{l} 2.7 \; V \leq E V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$			
		$\label{eq:VDD} \begin{array}{l} 2.4 \; V \leq E V_{DD} < 3.3 \; V , \; 1.6 \; V \leq V_b \leq 2.0 \; V \; \mbox{Note 3} , \\ C_b = 30 \; pF , \; R_b = 5.5 \; k\Omega \end{array}$			ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

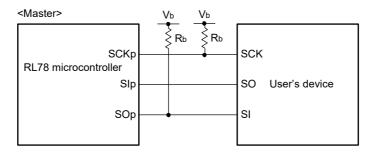
Note 3. Use it with $EV_{DD} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)



Simplified SPI (CSI) mode connection diagram (during communication at different potential)



Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

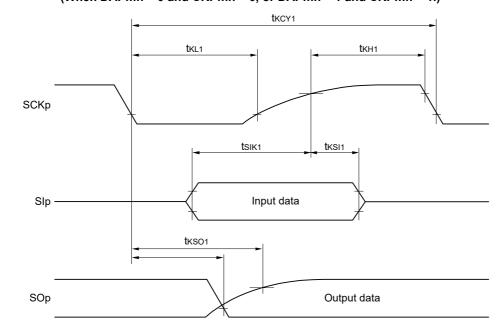
Remark 2. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

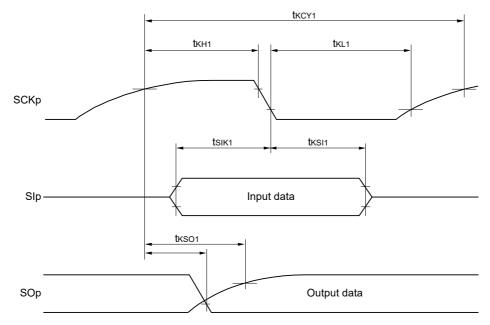
n: Channel number (mn = 00 to 03))





Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

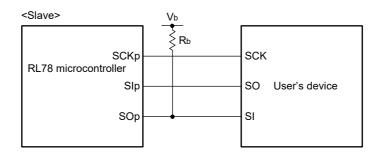
Descenter	O maked	0	-141	HS (high-spe	ed main) Mode	1.1 34
Parameter	Symbol	Con	ditions	MIN.	MAX.	Unit
SCKp cycle time Note 1	tксү2	$4.0~V \leq EV_{DD} \leq 5.5~V,$	$20 \text{ MHz} < f_{MCK} \leq 24 \text{ MHz}$	24/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	$8 \text{ MHz} < \text{fmck} \le 20 \text{ MHz}$	20/fмск		ns
			$4 \text{ MHz} < f_{MCK} \leq 8 \text{ MHz}$	16/fмск		ns
		-	fмск ≤ 4 MHz	12/fмск		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	20 MHz < fмск ≤ 24 MHz	32/fмск		ns
			16 MHz < fмск ≤ 20 MHz	28/fмск		ns
			$8 \text{ MHz} < \text{fmck} \le 16 \text{ MHz}$	24/fмск		ns
			$4 \text{ MHz} < \text{fmck} \le 8 \text{ MHz}$	16/fмск		ns
			fмск ≤ 4 MHz	12/fмск		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD}} < 3.3 \text{ V},$	20 MHz < fмск ≤ 24 MHz	72/fмск		ns
		$1.6~V \leq V_b \leq 2.0~V~Note~2$	$16 \text{ MHz} < \text{fmck} \le 20 \text{ MHz}$	64/fмск		ns
			8 MHz < fмск ≤ 16 MHz	52/fмск		ns
			$4 \text{ MHz} < \text{fmck} \le 8 \text{ MHz}$	32/fмск		ns
			fмск ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tkh2, tkl2	$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7$	$V \le V_b \le 4.0 V$	tксү2/2 - 24		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3$	$V \leq V_b \leq 2.7 \ V$	tксү2/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6$	$V \leq V_b \leq 2.0 \ V \ \text{Note 2}$	tксү2/2 - 100		ns
SIp setup time (to SCKp↑) ^{Note 3}	tsıĸ2	$2.7~V \leq EV_{DD} \leq 5.5~V,~2.3$	$V \leq V_b \leq 4.0 \ V$	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD}} < 3.3 \text{ V}, 1.6$	$V \leq V_b \leq 2.0~V$ Note 2	1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 4	tĸsı2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output ^{Note 5}	tkso2	$\begin{array}{l} 4.0 \ \text{V} \leq \text{EV}_{\text{DD}} \leq 5.5 \ \text{V}, 2.7 \\ \text{C}_{\text{b}} = 30 \ \text{pF}, \text{R}_{\text{b}} = 1.4 \ \text{k}\Omega \end{array}$	$V \leq V_b \leq 4.0 \ V$		2/fмск + 240	ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, 2.3 \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	$V \leq V_b \leq 2.7 \ V$		2/fмск + 428	ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	$V \leq V_b \leq 2.0 \ V$ Note 2		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)



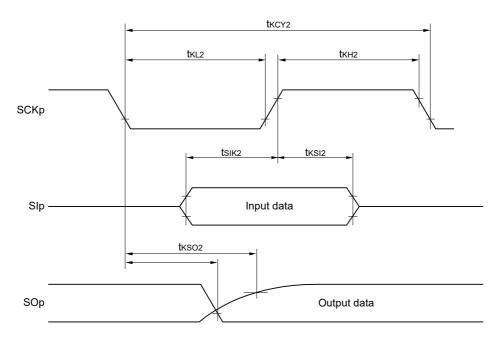
- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EV_{DD} \ge V_b$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

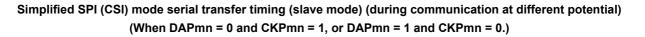


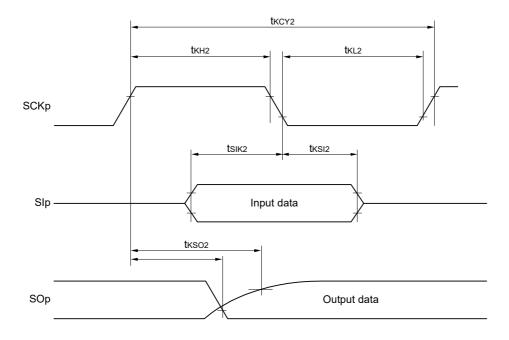
- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 3. fMCK: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))





Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

RL78/G11

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (simplified I²C mode)

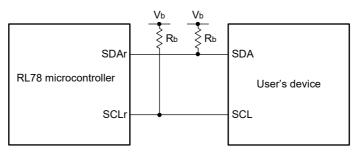
Parameter	Symbol	Conditions	HS (high-speed		Unit	
	Gymbol	Conditions	MIN.	MAX.	Onic	
SCLr clock frequency	fsc∟	$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_{b} \leq 4.0 \ V, \\ C_{b} = 50 \ pF, \ R_{b} = 2.7 \ k\Omega \end{array}$		400 Note 1	kHz	
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		400 Note 1	kHz	
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$		100 Note 1	kHz	
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		100 Note 1	kHz	
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		100 Note 1	kHz	
Hold time when SCLr = "L"	tLOW	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1200		ns	
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1200		ns	
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	4600		ns	
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	4600		ns	
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	4650		ns	
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{array}$	620		ns	
		$\begin{array}{l} 2.7 \ {\sf V} \leq {\sf EV}_{{\sf DD}} < 4.0 \ {\sf V}, \ 2.3 \ {\sf V} \leq {\sf V}_{{\sf b}} \leq 2.7 \ {\sf V}, \\ {\sf C}_{{\sf b}} = 50 \ {\sf pF}, \ {\sf R}_{{\sf b}} = 2.7 \ {\sf k}\Omega \end{array}$	500		ns	
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	2700		ns	
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ \mathbf{C}_{b} = 100 \; pF, R_{b} = 2.7 \; k\Omega \end{array}$	2400		ns	
		$\begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	1830		ns	
Data setup time (reception)	tsu:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/fмск + 340 Note 3		ns	
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ \mathbf{C}_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{array}$	1/fмск + 340 Note 3		ns	
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	1/fмск + 760 Note 3		ns	
		$\begin{array}{l} 2.7 \ V \leq EV_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/f _{MCK} + 760 Note 3		ns	
		$\label{eq:VDD} \begin{array}{l} 2.4 \ V \leq EV_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V \ \mbox{Note 2}, \\ C_b = 100 \ pF, \ R_b = 5.5 \ \mbox{k}\Omega \end{array}$	1/fмск + 570 Note 3		ns	
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \ V \leq {\sf EV}_{\sf DD} \leq 5.5 \ V, \ 2.7 \ V \leq {\sf V}_{\sf b} \leq 4.0 \ V, \\ C_{\sf b} = 50 \ p{\sf F}, \ R_{\sf b} = 2.7 \ {\sf k}\Omega \end{array}$	0	770	ns	
		$\begin{array}{l} 2.7 \ {\sf V} \leq {\sf EV}_{{\sf DD}} < 4.0 \ {\sf V}, \ 2.3 \ {\sf V} \leq {\sf V}_{{\sf b}} \leq 2.7 \ {\sf V}, \\ C_{{\sf b}} = 50 \ {\sf pF}, \ R_{{\sf b}} = 2.7 \ {\sf k}\Omega \end{array}$	0	770	ns	
		$\begin{array}{l} 4.0 \ V \leq EV_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{array}$	0	1420	ns	
		$\begin{array}{l} 2.7 \; V \leq EV_{DD} < 4.0 \; V, 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	1420	ns	

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

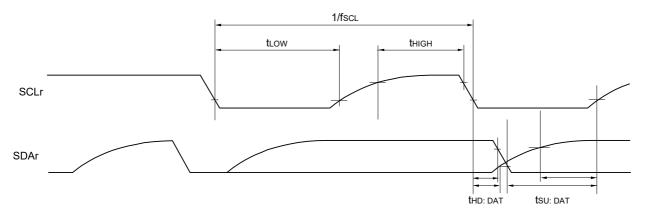


- **Note 1.** The value must be equal to or less than fMCK/4.
- Note 2. Use it with $EV_{DD} \ge V_b$.
- Note 3. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".
- Caution Select the TTL input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the N-ch open drain output (EVDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01, 10 and 11), g: PIM, POM number (g = 0, 3 and 5)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3), mn = 00 to 03)



3.5.2 Serial interface IICA

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS	3 (high-sp	eed main) i	mode	Unit
			Standa	rd mode	Fast	mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fcLk ≥ 3.5 MHz	_	—	0	400	kHz
		Standard mode: fc∟ĸ ≥ 1 MHz	0	100			kHz
Setup time of restart condition	tsu: STA		4.7		0.6		μs
Hold time ^{Note 1}	thd: STA		4.0		0.6		μs
Hold time when SCLA0 = "L"	t∟ow		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu: dat		250		100		ns
Data hold time (transmission) Note 2	thd: dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu: sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

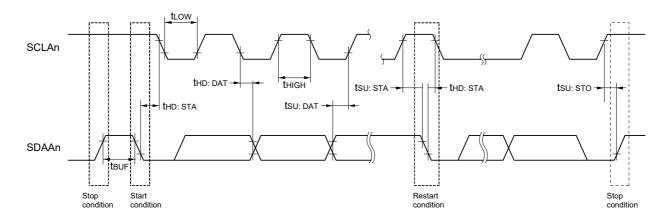
Note 2. The maximum value (MAX.) of the DEAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI3	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI22	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 and ANI3	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		and temperature sensor output voltage	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±0.25	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3	$2.4 \text{ V} \leq \text{AV}_{\text{REFP}} \leq 5.5 \text{ V}$			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}	$2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}$			±1.5	LSB
Analog input voltage	VAIN	ANI2 and ANI3		0		AVREFP	V
		Internal reference voltage (2.4 V \leq V _{DD} \leq 5.5 V)		١	V _{BGR} Note 4		V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V)		VTMPS25 Note 4		ie 4	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

 Note 3.
 When AVREFP < VDD, the MAX. values are as follows.</th>

 Overall error:
 Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

 Zero-scale error/Full-scale error:
 Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

 Integral linearity error/ Differential linearity error:
 Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

Parameter	Symbol	Conc	Conditions		TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution EVDD \leq AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	2.125		39	μs
		Target ANI pin: ANI16 to ANI22	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution EVDD ≤ AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±0.35	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution EVDD \leq AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution EVDD \leq AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution EVDD \leq AVREFP = VDD Notes 3, 4	$2.4~V \leq AV_{REFP} \leq 5.5~V$			±2.0	LSB
Analog input voltage	VAIN	ANI16 to ANI22	·	0		AVREFP and EVDD	V

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, VSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Excludes quantization error (±1/2 LSB). Note 1.

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD \leq AVREFP < VDD$, the MAX. values are as follows.

	Overall error:	Add ±1.0 LSB to the MAX. value when AVREFP = VDD.
	Zero-scale error/Full-scale error:	Add ±0.05%FSR to the MAX. value when AVREFP = VDD.
	Integral linearity error/ Differential linearity error:	Add ±0.5 LSB to the MAX. value when AVREFP = VDD.
Note 4.	When AVREFP < EVDD \leq VDD, the MAX. values an	e as follows.
	Overall error:	Add ±4.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error:

Add ±0.20%FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI3, ANI16 to ANI22	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
		temperature sensor output voltage	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI3		0		Vdd	V
		ANI16 to ANI22		0		EVDD	V
		Internal reference voltage $(2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$		\	/ _{BGR} Note 3		V
		Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V)		VTMPS25 Not		te 3	V

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VDD. Reference voltage (-) = Vss)

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0 to ANI3, ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, 2.4 V \leq EVDD \leq VDD = 0 V,

Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv		17		39	μs
Zero-scale error Notes 1, 2	Ezs				±0.60	% FSR
Integral linearity error Note 1	ILE				±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	Vain		0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.



3.6.2 Temperature sensor characteristics/internal reference voltage characteristic

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	Vbgr	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp	$2.4~V \leq V_{DD} \leq 3.6~V$	5			μs

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

3.6.3 D/A converter (channel 1)

(TA = -40 to +105°C, 2.4 V \leq EVss \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8	bit	
Overall error	AINL	Rload = 4 M Ω	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.5	LSB
		Rload = 8 M Ω	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7~V \leq V_{DD} \leq 5.5~V$			3	μs
			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$			6	μs



3.6.4 Comparator

(Comparator 0: TA = -40 to +105°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)
(Comparator 1: TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	VIREF0	IVREF0 pin	0		VDD - 1.4 Note 1	V	
	VIREF1	IVREF1 pin		1.4 Note 1		Vdd	V
	VICMP	IVCMP0 pin		-0.3		V _{DD} + 0.3	V
		IVCMP1 pin		-0.3		EV _{DD} + 0.3	V
Output delay	td	V _{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3		μs
			Comparator low-speed mode, window mode		4		μs
Operation stabilization wait time	tсмр			100			μs
Reference voltage declination in channel 0 of internal DAC ^{Note 2}	⊿VIDAC					±2.5	LSB

Note 1. In window mode, make sure that VREF1 - VREF0 \geq 0.2 V.

Note 2. Only in CMP0



3.6.5 PGA

Parameter	Symbol	Сог	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	Vipga			0		0.9 × V⊳⊳/Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{\text{DD}}$			V
	VIOLPGA				$0.07\times V_{\text{DD}}$	V	
Gain error		x4, x8				±1	%
		x16			±1.5	%	
		x32			±2	%	
Slew rate	to 0.9V₀₀/gain 10 to 90% of c	When VIN = 0.1Vpd/gain	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
		10 to 90% of output voltage amplitude	$4.0 V \le V_{DD} \le 5.5 V (x32)$	3.0			
			$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
	SRfpga	SR _{FPGA} Falling When VIN= 0.1V _{DD} /gain to 0.9V _{DD} /gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			
		90 to 10% of output	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} (x32)$	3.0			
		voltage amplitude	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 4.0 \text{V}$	0.5			
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time ^{Note}		x16, x32	(16, x32			10	μs

(TA = -40 to +105°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Note Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).



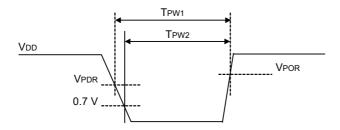
3.6.6 POR circuit characteristics

,	,					
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage VPOR The power s		The power supply voltage is rising.	1.45	1.51	1.57	V
	Vpdr	The power supply voltage is falling. Note 1	1.44	1.50	1.56	V
Minimum pulse width Note 2	TPW1	Other than STOP/SUB HALT/SUB RUN	300			μs
	TPW2	STOP/SUB HALT/SUB RUN	300			μs

(TA = -40 to +105°C, Vss = 0 V)

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.

Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





3.6.7 LVD circuit characteristics

(1) LVD Detection Voltage of Reset Mode and Interrupt Mode

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	VLVD0	The power supply voltage is rising.	3.90	4.06	4.22	V
			The power supply voltage is falling.	3.83	3.98	4.13	V
		VLVD1	The power supply voltage is rising.	3.60	3.75	3.90	V
			The power supply voltage is falling.	3.53	3.67	3.81	V
		VLVD2	The power supply voltage is rising.	3.01	3.13	3.25	V
			The power supply voltage is falling.	2.94	3.06	3.18	V
		VLVD3	The power supply voltage is rising.	2.90	3.02	3.14	V
			The power supply voltage is falling.	2.85	2.96	3.07	V
		VLVD4	The power supply voltage is rising.	2.81	2.92	3.03	V
			The power supply voltage is falling.	2.75	2.86	2.97	V
		VLVD5	The power supply voltage is rising.	2.71	2.81	2.92	V
			The power supply voltage is falling.	2.64	2.75	2.86	V
		VLVD6	The power supply voltage is rising.	2.61	2.71	2.81	V
			The power supply voltage is falling.	2.55	2.65	2.75	V
		VLVD7	The power supply voltage is rising.	2.51	2.61	2.71	V
			The power supply voltage is falling.	2.45	2.55	2.65	V
Minimum pulse widt	h	tLw		300			μs
Detection delay time						300	μs

(TA = -40 to +105°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

(2) LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol		Con	MIN.	TYP.	MAX.	Unit	
Interrupt and VLVDD0 VPOC0, VPOC1, VPOC2 = 0, 1, 1, falling reset voltage				2.64	2.75	2.86	V	
reset mode	VLVDD1		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3		LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.8 Power supply voltage rising slope characteristics

(TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.



3.7 RAM Data Retention Characteristics

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
ata rete	ention supply voltage	VDDDR		1.44 Note		5.5	V
ote	•		n voltage. When the voltage when a POR reset is effect	•	data is reta	ained before	a POR re
		}}	— STOP mode ———			Operation m	node
Vdi	D		 RAM data retention —— VDDDR 				_
	STOP instruction exec	ution		I			
	andby release signal errupt request))}		/			

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

3.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$		1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	TA = 85°C	100,000			
		Retained for 20 years	TA = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.



RL78/G11

3.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +105°C	2.4 $V \le EVDD \le VDD \le 5$.	5 V, Vss = 0 V)
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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

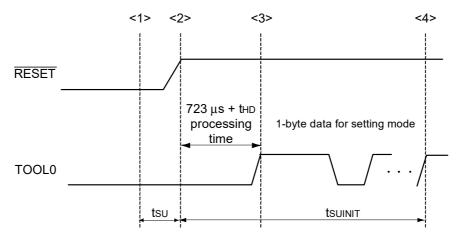
3.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified ^{Note 1}	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) ^{Notes 1, 2}	thd	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μ s).



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

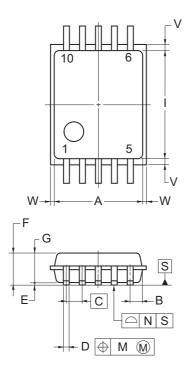
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.
 - tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
 - tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)



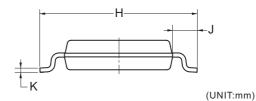
4. PACKAGE DRAWINGS

4.1 10-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP10-4.4x3.6-0.65	PLSP0010JA-A	P10MA-65-CAC-2	0.05



detail of lead end



NO	Т	E

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

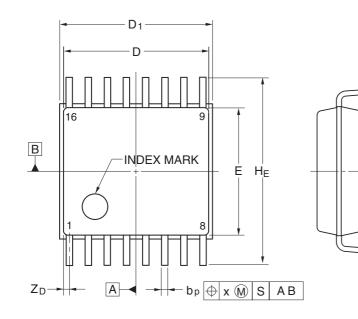
ITEM	DIMENSIONS
А	3.60±0.10
В	0.50
С	0.65 (T.P.)
D	0.24 ± 0.08
E	0.10±0.05
F	1.45 MAX.
G	1.20±0.10
Н	6.40±0.20
1	4.40±0.10
J	1.00±0.20
К	$0.17^{+0.08}_{-0.07}$
L	0.50
М	0.13
Ν	0.10
Р	$3^{\circ} + 5^{\circ} - 3^{\circ}$
Т	0.25 (T.P.)
U	0.60 ± 0.15
V	0.25 MAX.
W	0.15 MAX.

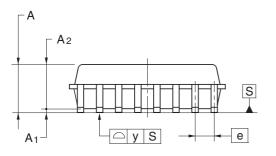
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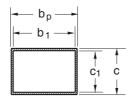
4.2 16-pin package

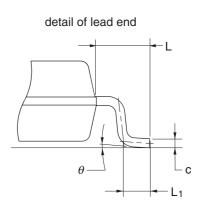
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-SSOP16-4.4x5-0.65	PRSP0016JC-B	P16MA-65-FAB	0.08





Terminal cross section

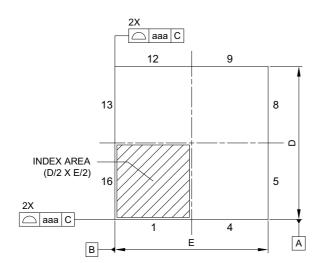


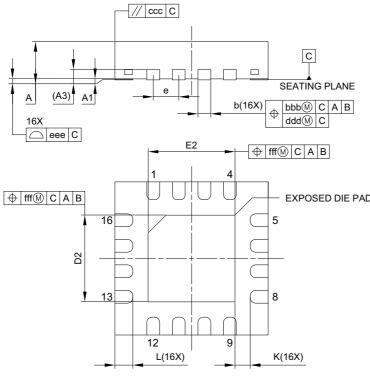


Referance	Dimension in Millimeters				
Symbol	Min	Nom	Max		
D	4.85	5.00	5.15		
D1	5.05	5.20	5.35		
E	4.20	4.40	4.60		
A ₂		1.50			
A ₁	0.075	0.125	0.175		
А			1.725		
bp	0.17	0.24	0.32		
b1		0.22			
С	0.14	0.17	0.20		
C ₁		0.15			
θ	0°		8°		
HE	6.20	6.40	6.60		
е		0.65			
х			0.13		
у			0.10		
Z _D		0.225			
L	0.35	0.50	0.65		
L ₁		1.00			



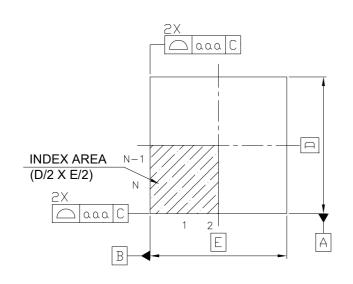
JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN016-3x3-0.50	PWQN0016KD-A	0.02

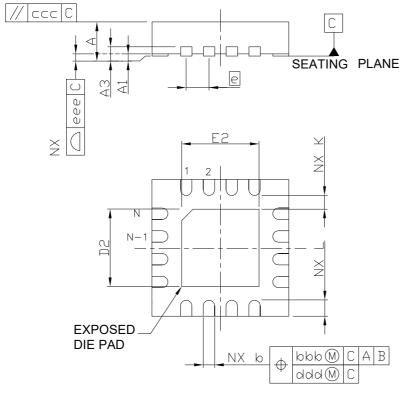




Reference	Dimension in Millimeters				
Symbol	Min.	Nom.	Max.		
А	_	_	0.80		
A1	0.00	0.02	0.05		
A3		0.203 REF			
b	0.20	0.25	0.30		
D		3.00 BSC			
E		3.00 BSC			
е		0.50 BSC			
L	0.30	0.35	0.40		
К	0.20	-	-		
D2	1.65	1.70	1.75		
E2	1.65	1.70	1.75		
aaa		0.15			
bbb		0.10			
CCC		0.10			
ddd		0.05 0.08			
eee					
fff		0.10			
	Symbol A A1 A3 b D E e C L K D2 E2 aaa bbb Cccc ddd eee	Ninelection A - A1 0.00 A3 0.20 D 1.65 E2 1.65 aaa 0.20 bbb 0.20 Cccc 0.20 dddd 0.20	Nome Min. Nom. A - - A1 0.00 0.02 A3 0.203 REF b 0.20 0.25 D 3.00 BSC E 3.00 BSC e 0.50 BSC L 0.30 0.35 K 0.20 - D2 1.65 1.70 E2 1.65 1.70 aaa 0.15 0.10 bbb 0.10 0.05 eee 0.10 0.05		

JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN16-3×3-0.50	PWQN0016KE-A	0.02



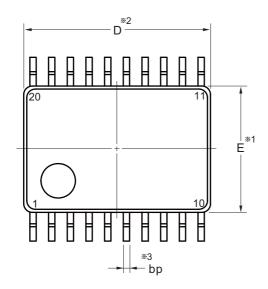


Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
А	—	—	0.80	
A ₁	0.00	—	0.05	
A ₃	0	.20 REF	=.	
b	0.20	0.25	0.30	
D		3.00	—	
E	_	3.00	_	
е	_	0.50	_	
N		16		
L	0.25	0.35	0.45	
К	0.20	—	_	
D ₂	1.60	1.70	1.80	
E ₂	1.60	1.70	1.80	
aaa	_	—	0.15	
bbb	_	—	0.10	
ccc	_	_	0.10	
ddd	_	_	0.05	
eee		—	0.08	

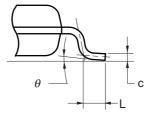


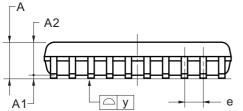
4.3 20-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



detail of lead end





NOTE

1.Dimensions "%1" and "%2" do not include mold flash.

2.Dimension "3" does not include trim offset.

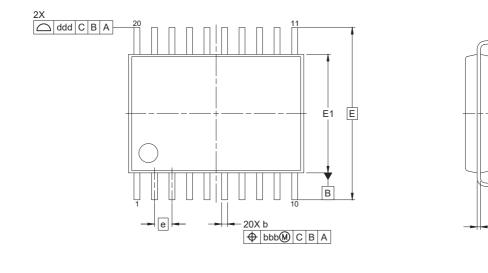
	— HE —	
\mathcal{I}		

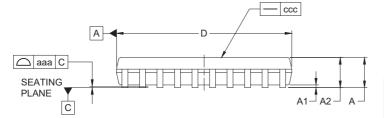
	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
А	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	0.22 + 0.10 - 0.05
С	$0.15 \pm 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°
θ	0° to 10°

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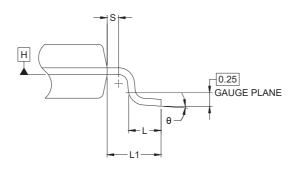


JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-TSSOP20-4.40x6.50-0.65	PTSP0020JI-A	0.08





Detail of Lead End



Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
А	-	-	1.20
A1	0.05	-	0.15
A2	0.80	1.00	1.05
b	0.19	-	0.30
С	0.09	0.127	0.20
D	6.40	6.50	6.60
E1	4.30	4.40	4.50
E	6.40 BSC		
е	0.65 BSC		
L1		1.00 REF	
L	0.50	0.60	0.75
S	0.20	-	-
θ	0°	-	8°
aaa	0.10		
bbb	0.10		
ссс		0.05	
ddd	0.20		

С

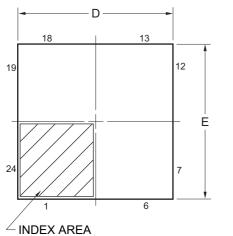
NOTES:

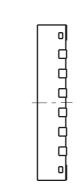
1.DIMENSION 'D' AND 'E1' DOES NOT INCLUDE MOLD FLASH. 2.DIMENSION 'b' DOES NOT INCLUDE TRIM OFFSET. 3.DIMENSION 'D' AND 'E1' TO BE DETERMINED AT DATUM PLANE [H].

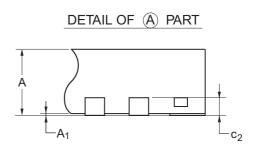


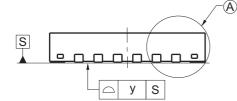
4.4 24-pin package

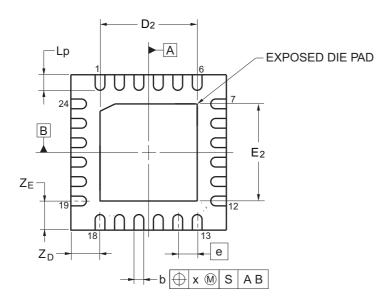
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-3	0.04









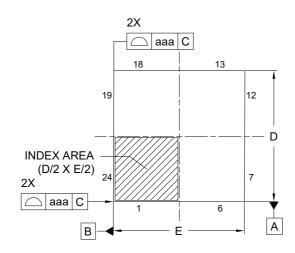


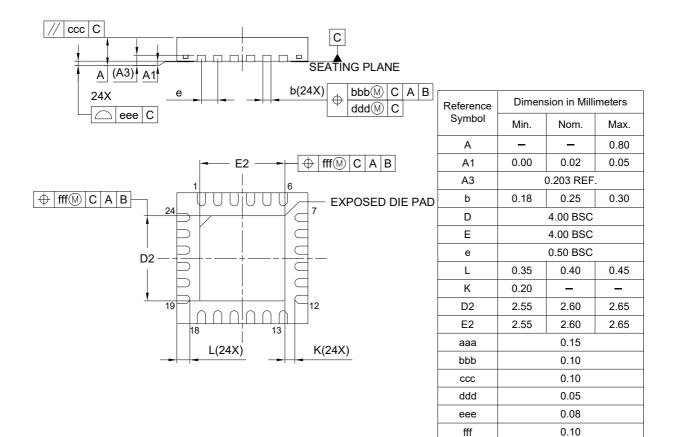
Referance	Dimens	Dimension in Millimeters		
Symbol	Min	Nom	Max	
D	3.95	4.00	4.05	
E	3.95	4.00	4.05	
A			0.80	
A ₁	0.00			
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
у			0.05	
ZD	_	0.75		
Z _E		0.75		
C ₂	0.15	0.20	0.25	
D ₂		2.50		
E ₂		2.50		

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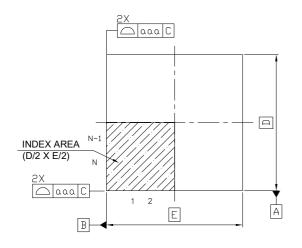
JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN024-4x4-0.50	PWQN0024KF-A	0.04

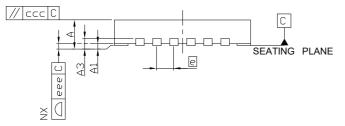


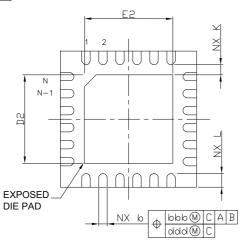




JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN24-4×4-0.50	PWQN0024KH-A	0.04





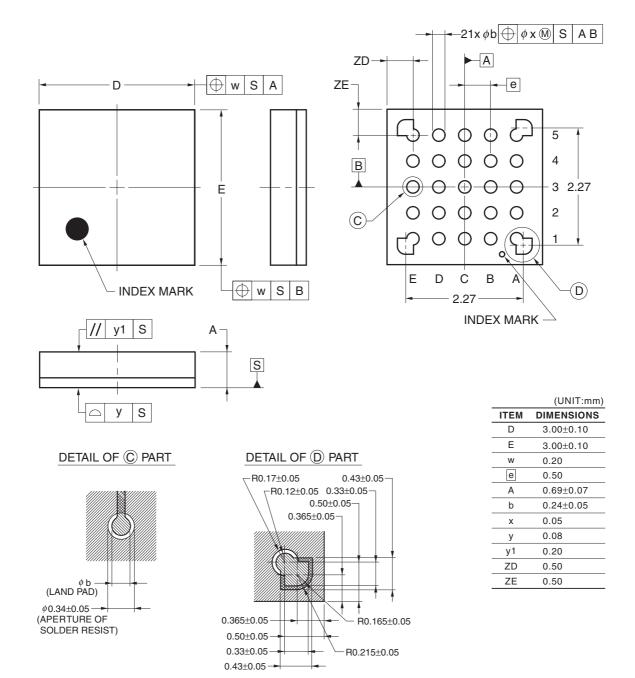


Reference	Dimens	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.	
A	_	_	0.80	
A ₁	0.00	_	0.05	
A ₃	0	.20 REF		
b	0.20	0.25	0.30	
D	_	4.00	_	
E	_	4.00	—	
е	_	0.50	_	
N		24		
L	0.30	0.40	0.50	
К	0.20	-	—	
D ₂	2.50	2.60	2.70	
E ₂	2.50	2.60	2.70	
aaa	_	—	0.15	
bbb	_	_	0.10	
ссс	—	—	0.10	
ddd	_	_	0.05	
eee	_	_	0.08	



4.5 25-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



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REVISION HISTORY

RL78/G11 Datasheet

Devi	Dete	Description	
Rev.	Date	Page	Summary
0.50	Mar 31 2016	—	First Edition issued
1.00	Sep 28 2016	p.7	Modification of Pin Configuration in 1.3.3 25-pin products
		p.9	Addition of 1.5.1 20-pin products
		p.10	Addition of product name and Modification of Block Diagram in 1.5.2 24-pin, 25- pin products
		p.12	Addition of I ² C bus in 1.6 Outline of Functions
		p.15	Modification of Conditions of IOH1, IOL1 in 2.1 Absolute Maximum Ratings
		p.16	Modification of High-speed on-chip oscillator clock frequency accuracy and addition of DIMT, DIMV in 2.2.2 On-chip oscillator characteristics
		p.17	Modification of Caution in 2.3.1 Pin characteristics
		p.19	Modification of Input voltage, high and Input voltage, low in 2.3.1 Pin characteristics
		p.19, 20	Modification of Caution in 2.3.1 Pin characteristics
		p.22, 23, 24, 26, 27	Modification of specifications in 2.3.2 Supply current characteristics
		p.29, 30	Modification of specification in 2.4 AC Characteristics
		p.35	Modification of specifications in 2.5.1 Serial array unit (1)
		p.39	Modification of specifications in 2.5.1 Serial array unit (3)
		p.40, 42	Modification of specification in 2.5.1 Serial array unit (4)
		p.62	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (1)
		p.64	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (2)
		p.65	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (3)
		p.70	Modification of Conditions in 2.6.2 Temperature sensor haracteristics/internal reference voltage characteristic
		p.79	Addition of description in 3 ELECTRICAL SPECIFICATIONS (TA = -40 to $+105^{\circ}$ C)
		p.82	Modification of High-speed on-chip oscillator clock frequency accuracy and addition of DIMT, DIMV in 3.2.2 On-chip oscillator characteristics
		p.83	Modification of Caution in 3.3.1 Pin characteristics
		p.85	Modification of Input voltage, high and Input voltage, low in 3.3.1 Pin characteristics
		p.85, 86	Modification of Caution in 3.3.1 Pin characteristics
		p.88 to 91	Modification of specifications in 3.3.2 Supply current characteristics
		p.97	Modification of specifications and specification table in 3.5.1 Serial array unit (1)
		p.103	Modification of specifications in 3.5.1 Serial array unit (3)
		p.125	Modification of Conditions in 3.6.1 A/D converter characteristics (4)
		p.126	Modification of Conditions in 3.6.2 Temperature sensor haracteristics/internal reference voltage characteristic
1.10	Dec 28 2016	p.4	Modification of 1.2 Ordering Information
2.00	Feb 15, 2018	Throughout	Addition of specifications of 10-pin and 16-pin products
		p.2	Modification of description in 1.1 Features
		p.6	Modification of figure in 1.3.4 24-pin products
		p.11	Modification of figure in 1.5.3 20-pin products
		p.12	Modification of figure in 1.5.4 24-pin, 25-pin products

Rev.	Date		Description
Nev.	Date	Page	Summary
2.00	Feb 15, 2018	p.13, 14	Modification of table in 1.6 Outline of Functions
		p.18	Modification of 2.2.2 On-chip oscillator characteristics
		p.19, 21	Modification of 2.3.1 Pin characteristics
		p.24	Modification of 2.3.2 Supply current characteristics
		p.32	Modification of 2.4 AC Characteristics
		p.79	Modification of figure in 2.10 Timing of Entry to Flash Memory Programming Modes
		p.84	Modification of 3.2.1 X1 characteristics
		p.84	Modification of 3.2.2 On-chip oscillator characteristics
		p.85, 86, 87	Modification of 3.3.1 Pin characteristics
		p.95	Modification of 3.4 AC Characteristics
		p.99	Modification of note in 3.5.1 Serial array unit (1)
		p.134	Modification of figure in 3.10 Timing of Entry to Flash Memory Programming Modes
2.20	Apr 26, 2019	p.3	Addition of note in Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.5	Modification of figure in 1.3.1 10-pin products
		p.5	Modification of figure in 1.3.2 16-pin products
		p.5	Modification of figure in 1.3.3 20-pin products
	p.6 p.13, 14		Modification of figure in 1.3.4 24-pin products
			Modification of table in 1.6 Outline of Functions
		p.16	Modification of specification in 2.1 Absolute Maximum Ratings
		p.19, 22	Modification of specification in 2.3.1 Pin characteristics
		p.25, 27	Modification of note 1 in 2.3.2 Supply current characteristics
		p.29, 30	Modification of specification and addition of note 14 in 2.3.2 Supply current characteristics, Peripheral Functions (Common to all products)
		p.32	Modification of specification in 2.4 AC Characteristics
		p.36	Modification of note 2 in 2.5.1 Serial array unit, (1) During communication at same potential (UART mode)
	p.41		Modification of specification in 2.5.1 Serial array unit, (3) During communication at same potential (CSI mode) (master mode, SCKp internal clock output), When P20 is used as SO10 pin
		p.43	Modification of specification in 2.5.1 Serial array unit, (4) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P01, P32, P53, P54 and P56 are used as SOmn pins
		p.44	Modification of specification in 2.5.1 Serial array unit, (4) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P20 is used as SO10 pin
		p.47	Modification of specification in 2.5.1 Serial array unit, (5) During communication at same potential (simplified I ² C mode)
		p.53, 54	Modification of specification in 2.5.1 Serial array unit, (7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (CSI mode) (master mode, SCKp internal clock output, corresponding CSI00 only)
		p.60	Modification of note 3 in 2.5.1 Serial array unit, (9) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (CSI mode) (slave mode, SCKp external clock input)

Rev.	Date	Description	
NCV.	Date	Page	Summary
2.20	Apr 26, 2019	p.69	Modification of note 3 in 2.6.1 A/D converter characteristics, (2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22
		p.70	Modification of specification in 2.6.1 A/D converter characteristics, (3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = VSS (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage
		p.71	Modification of specification in 2.6.1 A/D converter characteristics, (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 and ANI3, ANI16 to ANI22
		p.72	Modification of title in 2.6.3 D/A converter (channel 1)
		p.73	Modification of specification in 2.6.4 Comparator
		p.82	Modification of specification in 3.1 Absolute Maximum Ratings
		p.84	Modification of specification in 3.2.1 X1 characteristics
		p.85, 87, 88	Modification of specification in 3.3.1 Pin characteristics
		p.93	Modification of specification in 3.3.2 Supply current characteristics, Peripheral Functions (Common to all products)
		p.99	Modification of specification in 3.5.1 Serial array unit, (1) during communication at same potential (UART mode), When P20 is used as TxD1 pin
		p.101	Modification of specification in 3.5.1 Serial array unit, (2) During communication at same potential (CSI mode) (master mode, SCKp internal clock output), When P01, P32, P53, P54 and P56 are used as Somn pins
		p.102	Modification of specification in 3.5.1 Serial array unit, (2) During communication at same potential (CSI mode) (master mode, SCKp internal clock output), When P20 is used as SO10 pin
		p.103	Modification of note 1 in 3.5.1 Serial array unit, (3) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P01, P32, P53, P54 and P56 are used as SOmn pins
		p.105	Modification of specification and note 1 in 3.5.1 Serial array unit, (3) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P20 is used as SO10 pin
		p.124	Modification of specification in 3.6.1 A/D converter characteristics, (1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage
		p.125	Modification of note 3 in 3.6.1 A/D converter characteristics, (2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22
		p.127	Modification of specification in 3.6.1 A/D converter characteristics, (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0 to ANI3, ANI16 to ANI22
		p.128	Modification of title in 3.6.3 D/A converter (channel 1)
		p.129	Modification of specification in 3.6.4 Comparator
		p.131	Modification of specification in 3.6.6 POR circuit characteristics
		p.132	Modification of specification in 3.6.7 LVD circuit characteristics, (1) LVD Detection Voltage of Reset Mode and Interrupt Mode

Rev.	Date	Description	
		Page	Summary
2.30	June 30, 2020	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.4	Modification of table in 1.2 Ordering Information
		p.5	Modification of description in 1.3.3 20-pin products
		p.26	Modification of specification in 2.3.2 Supply current characteristics
		p.138	Addition of package drawing in 4.3 20-pin package
		p.140	Addition of package drawing in 4.4 24-pin package
2.40	Oct 30, 2020	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.4	Modification of table in 1.2 Ordering Information
		p.6	Addition of description and figure in 1.3.2 16-pin products
		p.138	Addition of package drawing in 4.2 16-pin package
2.50	Mar 20, 2023	All	The module name for CSI was changed to Simplified SPI (CSI)
		All	"wait" for IIC was modified to "clock stretch"
		p.2	Addition of Note 1 in 1 Features
		p.4	Addition of Table Title and modification of Table 1-1 List of Ordering Part Numbers
		p.26	Modification of Note 1 in Table (TA = -40 to +85°C, 1.6 V ≤ EEVDD ≤ VDD ≤ 5.5 V, VSS = 0
			V) (2/4) of 2.3.2 Supply current characteristics
		p.28	Modification of Note 1 in Table (TA = -40 to +85°C, $1.6 \text{ V} \le \text{EEV}$ DD $\le \text{VDD} \le 5.5 \text{ V}$, Vss = 0
			V) (3/4) of 2.3.2 Supply current characteristics
		p.29	Modification of Note 1 in Table (TA = -40 to +85°C, $1.6 \text{ V} \le \text{EEV}_{DD} \le \text{V}_{DD} \le 5.5 \text{ V}$, Vss = 0
			V) (4/4) of 2.3.2 Supply current characteristics
		p.91	Modification of Note 1 in Table (TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0
			V)) (1/3) of 2.3.2 Supply current characteristics
		p.92	Modification of Note 1 in Table (TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)) (2/3) of 2.3.2 Supply current characteristics
		p.93	Modification of Note 1 in Table (TA = -40 to +105°C, $2.4 \text{ V} \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}$, Vss = 0
		p.00	V)) (3/3) of 2.3.2 Supply current characteristics
		p.139	Addition of package drawing in 4.2 16-pin Package
		p.144	Addition of package drawing in 4.4 24-pin Package
2.60	Mar 29, 2024	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
	-,	p.4	Modification of Table 1 - 1 List of Ordering Part Numbers

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General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power is supplied until the power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a systemevaluation test for the given product.

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